

# AMC3301 高精度、 $\pm 250\text{mV}$ 入力、強化絶縁アンプ DC/DC コンバータ内蔵

## 1 特長

- 3.3V または 5V 単一電源、DC/DC コンバータ内蔵
- シャント抵抗による電流測定用に最適化された  $\pm 250\text{mV}$  の入力電圧範囲
- 固定ゲイン: 8.2
- 小さい DC 誤差:
  - オフセット電圧:  $\pm 150\mu\text{V}$  (最大値)
  - オフセットドリフト:  $\pm 1\mu\text{V}/^\circ\text{C}$  (最大値)
  - ゲイン誤差:  $\pm 0.2\%$  (最大値)
  - ゲイン誤差ドリフト:  $\pm 40\text{ppm}/^\circ\text{C}$  (最大値)
  - 非線形性:  $\pm 0.04\%$  (最大値)
- 高 CMTI:  $85\text{kV}/\mu\text{s}$  (最小値)
- システム レベル診断機能
- CISPR-11 および CISPR-25 EMI 規格に準拠
- 安全関連認証:
  - DIN EN IEC 60747-17 (VDE 0884-17) に準拠した強化絶縁耐圧:  $6000\text{V}_{\text{PK}}$
  - UL 1577 に準拠した絶縁耐圧:  $4250\text{V}_{\text{RMS}}$  (1 分間)
- 拡張産業温度範囲の全体にわたって完全に仕様を規定:  $-40^\circ\text{C} \sim +125^\circ\text{C}$

## 2 アプリケーション

- 次の用途における絶縁型シャント・ベース電流センシング
  - 保護リレー
  - モーター・ドライブ
  - 電源
  - 太陽光発電インバータ

## 3 説明

AMC3301 は、シャントによる電流測定に最適化された高精度絶縁型アンプです。完全に統合された絶縁型 DC/DC コンバータのおかげで、本デバイスの低電圧側から電力を供給する単一電源動作が可能であるため、スペースに制約があるアプリケーション向けのユニークなソリューションとして活用できます。この容量性強化絶縁バリアは、DIN EN IEC 60747-17 (VDE 0884-17) および UL1577 により認証済みであり、最大  $1.2\text{kV}_{\text{RMS}}$  の作動電圧に対応しています。

この絶縁バリアは、異なる同相電圧レベルで動作するシステム領域を分離し、危険な電圧と損傷から低電圧側を保護します。

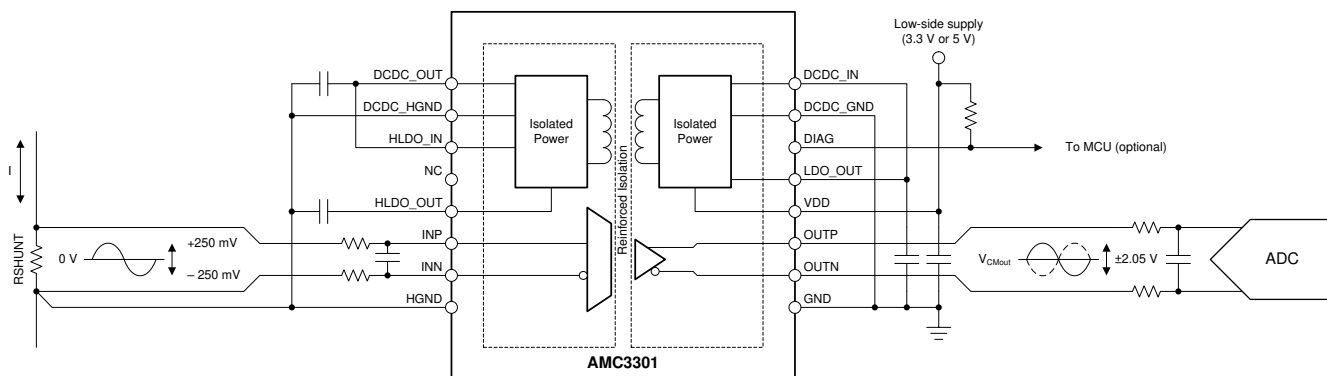
AMC3301 の入力は、低インピーダンスのシャント抵抗またはその他の信号レベルが小さい低インピーダンス電圧源と直接接続できるように最適化されています。優れた DC 精度と小さい温度ドリフトにより、拡張産業用温度範囲 ( $-40^\circ\text{C} \sim +125^\circ\text{C}$ ) にわたる高精度電流測定に対応できます。

AMC3301 の内蔵 DC/DC コンバータ フォルト検出および診断出力ピンを使用すると、システム レベルの設計と診断を簡素化できます。

### パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ (2)
AMC3301	DWE (SOIC, 16)	$10.3\text{mm} \times 10.3\text{mm}$

- 詳細については、[メカニカル](#)、[パッケージ](#)、および[注文情報](#)をご覧ください。
- パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



代表的なアプリケーション



## Table of Contents

<b>1 特長</b> .....	<b>1</b>	6.2 Functional Block Diagram.....	<b>18</b>
<b>2 アプリケーション</b> .....	<b>1</b>	6.3 Feature Description.....	<b>18</b>
<b>3 説明</b> .....	<b>1</b>	6.4 Device Functional Modes.....	<b>22</b>
<b>4 Pin Configuration and Functions</b> .....	<b>3</b>	<b>7 Application and Implementation</b> .....	<b>23</b>
<b>5 Specifications</b> .....	<b>4</b>	7.1 Application Information.....	<b>23</b>
5.1 Absolute Maximum Ratings.....	<b>4</b>	7.2 Typical Application.....	<b>23</b>
5.2 ESD Ratings.....	<b>4</b>	7.3 Best Design Practices.....	<b>27</b>
5.3 Recommended Operating Conditions.....	<b>4</b>	7.4 Power Supply Recommendations.....	<b>27</b>
5.4 Thermal Information.....	<b>5</b>	7.5 Layout.....	<b>29</b>
5.5 Power Ratings.....	<b>5</b>	<b>8 Device and Documentation Support</b> .....	<b>30</b>
5.6 Insulation Specifications.....	<b>6</b>	8.1 Device Support.....	<b>30</b>
5.7 Safety-Related Certifications.....	<b>7</b>	8.2 Documentation Support.....	<b>30</b>
5.8 Safety Limiting Values.....	<b>7</b>	8.3 Receiving Notification of Documentation Updates... <b>30</b>	
5.9 Electrical Characteristics.....	<b>8</b>	8.4 サポート・リソース.....	<b>30</b>
5.10 Switching Characteristics.....	<b>10</b>	8.5 Trademarks.....	<b>30</b>
5.11 Timing Diagram.....	<b>10</b>	8.6 静電気放電に関する注意事項.....	<b>30</b>
5.12 Insulation Characteristics Curves.....	<b>11</b>	8.7 用語集.....	<b>30</b>
5.13 Typical Characteristics.....	<b>12</b>	<b>9 Revision History</b> .....	<b>31</b>
<b>6 Detailed Description</b> .....	<b>18</b>	<b>10 Mechanical, Packaging, and Orderable Information</b> .....	<b>31</b>
6.1 Overview.....	<b>18</b>		

## 4 Pin Configuration and Functions

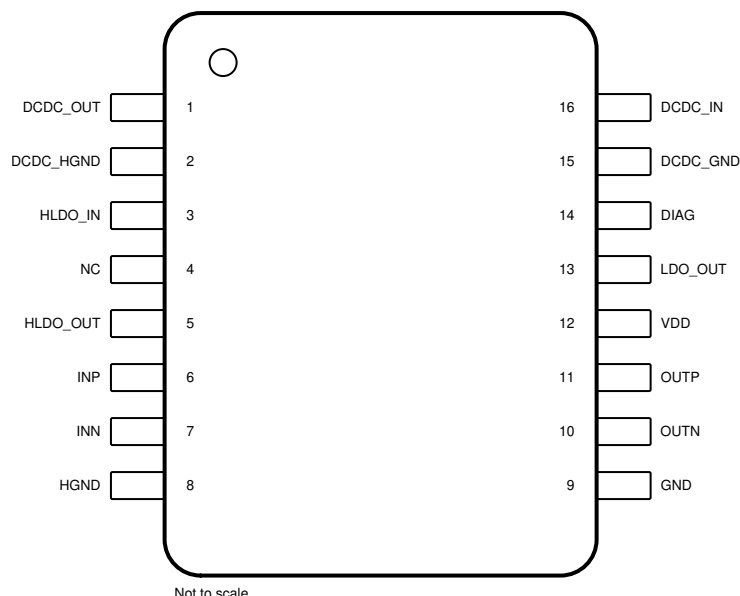


図 4-1. DWE Package, 16-Pin SOIC, Top View

表 4-1. Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	DCDC_OUT	Power	High-side output of the isolated DC/DC converter; connect this pin to the HLDO_IN pin. <sup>(1)</sup>
2	DCDC_HGND	High-side power ground	High-side ground reference for the isolated DC/DC converter; connect this pin to the HGND pin.
3	HLDO_IN	Power	Input of the high-side LDO; connect this pin to the DCDC_OUT pin. <sup>(1)</sup>
4	NC	—	No internal connection; connect this pin to HGND or leave this pin unconnected.
5	HLDO_OUT	Power	Output of the high-side LDO. <sup>(1)</sup>
6	INP	Analog input	Noninverting analog input. Either INP or INN must have a DC current path to HGND to define the common-mode input voltage. <sup>(2)</sup>
7	INN	Analog input	Inverting analog input. Either INP or INN must have a DC current path to HGND to define the common-mode input voltage. <sup>(2)</sup>
8	HGND	High-side signal ground	High-side analog ground; connect this pin to the DCDC_HGND pin.
9	GND	Low-side signal ground	Low-side analog ground; connect this pin to the DCDC_GND pin.
10	OUTN	Analog output	Inverting analog output.
11	OUTP	Analog output	Noninverting analog output.
12	VDD	Low-side power	Low-side power supply. <sup>(1)</sup>
13	LDO_OUT	Power	Output of the low-side LDO; connect this pin to the DCDC_IN pin. The output of the LDO must not be loaded by external circuitry. <sup>(1)</sup>
14	DIAG	Digital output	Active-low, open-drain status indicator output; connect this pin to the pullup supply (for example, VDD) using a resistor or leave this pin floating if not used.
15	DCDC_GND	Low-side power ground	Low-side ground reference for the isolated DC/DC converter; connect this pin to the GND pin.
16	DCDC_IN	Power	Low-side input of the isolated DC/DC converter; connect this pin to the LDO_OUT pin. <sup>(1)</sup>

(1) See the [Power Supply Recommendations](#) section for power-supply decoupling recommendations.

(2) See the [Layout](#) section for details.

## 5 Specifications

### 5.1 Absolute Maximum Ratings

see (1)

		MIN	MAX	UNIT
Power-supply voltage	VDD to GND	−0.3	6.5	V
Analog input voltage	INP, INN	HGND − 6	$V_{HLDO\_OUT} + 0.5$	V
Analog output voltage	OUTP, OUTN	GND − 0.5	VDD + 0.5	V
Digital output voltage	DIAG	GND − 0.5	6.5	V
Input current	Continuous, any pin except power-supply pins	−10	10	mA
Temperature	Junction, $T_J$		150	°C
	Storage, $T_{stg}$	−65	150	

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime

### 5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per per ANSI/ESDA/JEDEC JS-002(2)	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.  
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
<b>POWER SUPPLY</b>						
VDD	Low-side power supply	VDD to GND	3	3.3	5.5	V
<b>ANALOG INPUT</b>						
$V_{Clipping}$	Differential input voltage before clipping output	$V_{IN} = V_{INP} - V_{INN}$		±320		mV
$V_{FSR}$	Specified linear differential full-scale voltage	$V_{IN} = V_{INP} - V_{INN}$	−250		250	mV
	Absolute common-mode input voltage (1)	$(V_{INP} + V_{INN}) / 2$ to HGND	−2		$V_{HLDO\_OUT}$	V
$V_{CM}$	Operating common-mode input voltage	$(V_{INP} + V_{INN}) / 2$ to HGND	−0.16		1	V
<b>ANALOG OUTPUT</b>						
$C_{LOAD}$	Capacitive load	On OUTP or OUTN to GND2, Without any series resistance			500	pF
$C_{LOAD}$	Capacitive load	OUTP to OUTN, Without any series resistance			250	pF
$R_{LOAD}$	Resistive load	On OUTP or OUTN to GND2		10	1	kΩ
<b>DIGITAL OUTPUT</b>						
	Pull-up supply-voltage for DIAG pin		0		VDD	V
<b>TEMPERATURE RANGE</b>						
$T_A$	Specified ambient temperature		−40		125	°C

- (1) Steady-state voltage supported by the device in case of a system failure. See specified common-mode input voltage  $V_{CM}$  for normal operation. Observe analog input voltage range as specified in the *Absolute Maximum Ratings* table.

## 5.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		AMC3301	UNIT
		DWE (SOIC)	
		16 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	73.5	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	31	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	44	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	16.7	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	42.8	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 5.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P <sub>D</sub>	Maximum power dissipation	VDD = 5.5 V			231	mW
		VDD = 3.6 V			151	

## 5.6 Insulation Specifications

over operating ambient temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance <sup>(1)</sup>	Shortest pin-to-pin distance through air	≥ 8	mm
CPG	External creepage <sup>(1)</sup>	Shortest pin-to-pin distance across the package surface	≥ 8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance - capacitive signal isolation)	≥ 21	μm
		Minimum internal gap (internal clearance - transformer power isolation)	≥ 120	
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	≥ 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 600 V <sub>RMS</sub>	I-III	
		Rated mains voltage ≤ 1000 V <sub>RMS</sub>	I-II	
DIN EN IEC 60747-17 (VDE 0884-17) <sup>(2)</sup>				
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	At AC voltage	1700	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum-rated isolation working voltage	At AC voltage (sine wave)	1200	V <sub>RMS</sub>
		At DC voltage	1700	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	V <sub>TEST</sub> = V <sub>IOTM</sub> , t = 60s (qualification test), V <sub>TEST</sub> = 1.2 × V <sub>IOTM</sub> , t = 1s (100% production test)	6000	V <sub>PK</sub>
V <sub>IMP</sub>	Maximum impulse voltage <sup>(3)</sup>	Tested in air, 1.2/50μs waveform per IEC 62368-1	7700	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>(4)</sup>	Tested in oil (qualification test), 1.2/50μs waveform per IEC 62368-1	10000	V <sub>PK</sub>
q <sub>pd</sub>	Apparent charge <sup>(5)</sup>	Method a, after input/output safety test subgroups 2 and 3, V <sub>pd(ini)</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60s, V <sub>pd(m)</sub> = 1.2 × V <sub>IORM</sub> , t <sub>m</sub> = 10s	≤ 5	pC
		Method a, after environmental tests subgroup 1, V <sub>pd(ini)</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60s, V <sub>pd(m)</sub> = 1.6 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	
		Method b1, at preconditioning (type test) and routine test, V <sub>pd(ini)</sub> = 1.2 x V <sub>IOTM</sub> , t <sub>ini</sub> = 1s, V <sub>pd(m)</sub> = 1.875 × V <sub>IORM</sub> , t <sub>m</sub> = 1s	≤ 5	
		Method b2, at routine test (100% production) <sup>(7)</sup> , V <sub>pd(ini)</sub> = V <sub>pd(m)</sub> = 1.2 x V <sub>IOTM</sub> , t <sub>ini</sub> = t <sub>m</sub> = 1s	≤ 5	pC
C <sub>IO</sub>	Barrier capacitance, input to output <sup>(6)</sup>	V <sub>IO</sub> = 0.5 V <sub>PP</sub> at 1MHz	≅ 4.5	pF
R <sub>IO</sub>	Insulation resistance, input to output <sup>(6)</sup>	V <sub>IO</sub> = 500 V at T <sub>A</sub> = 25°C	> 10 <sup>12</sup>	Ω
		V <sub>IO</sub> = 500 V at 100°C ≤ T <sub>A</sub> ≤ 125°C	> 10 <sup>11</sup>	
		V <sub>IO</sub> = 500 V at T <sub>S</sub> = 150°C	> 10 <sup>9</sup>	
	Pollution degree		2	
	Climatic category		40/125/21	
UL1577				
V <sub>ISO</sub>	Withstand isolation voltage	V <sub>TEST</sub> = V <sub>ISO</sub> , t = 60 s (qualification test), V <sub>TEST</sub> = 1.2 × V <sub>ISO</sub> , t = 1 s (100% production test)	4250	V <sub>RMS</sub>

- (1) Apply creepage and clearance requirements according to the specific equipment isolation standards of an application. Care must be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board (PCB) do not reduce this distance. Creepage and clearance on a PCB become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a PCB are used to help increase these specifications.
- (2) This coupler is suitable for *safe electrical insulation* only within the safety ratings. Compliance with the safety ratings must be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air to determine the surge immunity of the package.
- (4) Testing is carried in oil to determine the intrinsic surge immunity of the isolation barrier.
- (5) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (6) All pins on each side of the barrier are tied together, creating a two-pin device.
- (7) Either method b1 or b2 is used in production.

## 5.7 Safety-Related Certifications

VDE	UL
DIN EN IEC 60747-17 (VDE 0884-17), EN IEC 60747-17, DIN EN IEC 62368-1 (VDE 0868-1), EN IEC 62368-1, IEC 62368-1 Clause : 5.4.3 ; 5.4.4.4 ; 5.4.9	Recognized under 1577 component recognition and CSA component acceptance NO 5 programs
Reinforced insulation	Single protection
Certificate number: 40040142	File number: E181974

## 5.8 Safety Limiting Values

Safety limiting <sup>(1)</sup> intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Safety input, output, or supply current	R <sub>θJA</sub> = 73.5°C/W, VDD = 5.5 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			309	mA
		R <sub>θJA</sub> = 73.5°C/W, VDD = 3.6 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			472	
P <sub>S</sub>	Safety input, output, or total power	R <sub>θJA</sub> = 73.5°C/W, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			1700	mW
T <sub>S</sub>	Maximum safety temperature				150	°C

- (1) The maximum safety temperature, T<sub>S</sub>, has the same value as the maximum junction temperature, T<sub>J</sub>, specified for the device. The I<sub>S</sub> and P<sub>S</sub> parameters represent the safety current and safety power, respectively. Do not exceed the maximum limits of I<sub>S</sub> and P<sub>S</sub>. These limits vary with the ambient temperature, T<sub>A</sub>.  
The junction-to-air thermal resistance, R<sub>θJA</sub>, in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:  
T<sub>J</sub> = T<sub>A</sub> + R<sub>θJA</sub> × P, where P is the power dissipated in the device.  
T<sub>J(max)</sub> = T<sub>S</sub> = T<sub>A</sub> + R<sub>θJA</sub> × P<sub>S</sub>, where T<sub>J(max)</sub> is the maximum junction temperature.  
P<sub>S</sub> = I<sub>S</sub> × VDD<sub>max</sub>, where VDD<sub>max</sub> is the maximum low-side voltage.

## 5.9 Electrical Characteristics

minimum and maximum specifications apply from  $T_A = -40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ,  $V_{DD} = 3.0\text{ V}$  to  $5.5\text{ V}$ ,  $\text{INP} = -250\text{ mV}$  to  $+250\text{ mV}$ ,  $\text{INN} = \text{HGND} = 0\text{ V}$ , and the external components listed in the *Typical Application* section; typical specifications are at  $T_A = 25^{\circ}\text{C}$ , and  $V_{DD} = 3.3\text{ V}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
R <sub>IN</sub>	Single-ended input resistance	INN = HGND	19			kΩ
R <sub>IND</sub>	Differential input resistance		22			
I <sub>IB</sub>	Input bias current	INP = INN = HGND; I <sub>IB</sub> = (I <sub>IBP</sub> + I <sub>IBN</sub> ) / 2	–41	–30	–24	μA
TCI <sub>IB</sub>	Input bias current drift		0.8			nA/°C
I <sub>IO</sub>	Input offset current	I <sub>IO</sub> =  I <sub>IBP</sub> – I <sub>IBN</sub>	1.4			nA
C <sub>IN</sub>	Single-ended input capacitance	INN = HGND, f <sub>IN</sub> = 275 kHz	2			pF
C <sub>IND</sub>	Differential input capacitance	f <sub>IN</sub> = 275 kHz	1			
ANALOG OUTPUT						
	Nominal gain		8.2			V/V
V <sub>CMout</sub>	Common-mode output voltage		1.39	1.44	1.49	V
V <sub>CLIPout</sub>	Clipping differential output voltage	V <sub>OUT</sub> = (V <sub>OUTP</sub> – V <sub>OUTN</sub> );  V <sub>IN</sub>   =  V <sub>INP</sub> – V <sub>INN</sub>   > V <sub>Clipping</sub>	±2.49			V
V <sub>Failsafe</sub>	Failsafe differential output voltage	V <sub>OUT</sub> = (V <sub>OUTP</sub> – V <sub>OUTN</sub> ); V <sub>DCDC_OUT</sub> ≤ V <sub>DCDCUV</sub> , or V <sub>HLD0_OUT</sub> ≤ V <sub>HLD0UV</sub>	–2.57      -2.5			V
BW	Output bandwidth		290	334		kHz
R <sub>OUT</sub>	Output resistance	On OUTP or OUTN	0.2			Ω
	Output short-circuit current	On OUTP or OUTN, sourcing or sinking, INP = INN = HGND, outputs shorted to either GND or VDD	14			mA
CMTI	Common-mode transient immunity	HGND – GND  = 2 kV	85	135		kV/μs
ACCURACY						
V <sub>OS</sub>	Input offset voltage <sup>(1) (2)</sup>	T <sub>A</sub> = 25°C, INP = INN = HGND	–0.15	±0.02	0.15	mV
TCV <sub>OS</sub>	Input offset drift <sup>(1) (2) (4)</sup>		–1	±0.15	1	μV/°C
E <sub>G</sub>	Gain error <sup>(1)</sup>	T <sub>A</sub> = 25°C	–0.2%	±0.04%	0.2%	
TCE <sub>G</sub>	Gain error drift <sup>(1) (5)</sup>		–40	±6	40	ppm/°C
	Nonlinearity <sup>(1)</sup>		–0.04%	±0.002%	0.04%	
	Nonlinearity drift <sup>(1)</sup>		0.9			ppm/°C
SNR	Signal-to-noise ratio	V <sub>IN</sub> = 0.5 V <sub>PP</sub> , f <sub>IN</sub> = 1 kHz, BW = 10 kHz, 10 kHz filter	80	85		dB
		V <sub>IN</sub> = 0.5 V <sub>PP</sub> , f <sub>IN</sub> = 10 kHz, BW = 100 kHz, 1 MHz filter	67	71		
THD	Total harmonic distortion <sup>(3)</sup>	V <sub>IN</sub> = 0.5 V <sub>pp</sub> , f <sub>IN</sub> = 10 kHz, BW = 100 kHz	–85			dB
	Output noise	INP = INN = HGND, f <sub>IN</sub> = 0 Hz, BW = 100 kHz	300			μV <sub>RMS</sub>
CMRR	Common-mode rejection ratio	f <sub>IN</sub> = 0 Hz, V <sub>CM min</sub> ≤ V <sub>CM</sub> ≤ V <sub>CM max</sub>	–97			dB
		f <sub>IN</sub> = 10 kHz, V <sub>CM min</sub> ≤ V <sub>CM</sub> ≤ V <sub>CM max</sub>	–98			
PSRR	Power-supply rejection ratio	VDD from 3.0 V to 5.5 V, at dc, input referred	–109			dB
		INP = INN = HGND, VDD from 3.0 V to 5.5 V, 10 kHz / 100 mV ripple, input referred	–98			



## 5.9 Electrical Characteristics (続き)

minimum and maximum specifications apply from  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ ,  $V_{DD} = 3.0\text{ V}$  to  $5.5\text{ V}$ ,  $I_{NP} = -250\text{ mV}$  to  $+250\text{ mV}$ ,  $I_{NN} = \text{HGND} = 0\text{ V}$ , and the external components listed in the *Typical Application* section; typical specifications are at  $T_A = 25^\circ\text{C}$ , and  $V_{DD} = 3.3\text{ V}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>DIGITAL OUTPUT (DIAG)</b>						
$V_{OL}$	Low-level output voltage	$I_{SINK} = 4\text{ mA}$		80	250	mV
$I_{LKG}$	Open-drain output leakage current	$V_{DD} = 5\text{ V}$		5	100	nA
<b>POWER SUPPLY</b>						
$I_{DD}$	Low-side supply current	no external load on HLDO		27.5	40	mA
		1 mA external load on HLDO		29.5	42	
$V_{DDUV}$	VDD analog undervoltage detection threshold	VDD rising			2.9	V
		VDD falling			2.8	
$V_{DDPOR}$	VDD digital reset threshold	VDD rising			2.5	V
		VDD falling			2.4	
$V_{DCDC\_OUT}$	DCDC output voltage	DCDC_OUT to HGND	3.1	3.5	4.65	V
$V_{DCDCUV}$	DCDC output undervoltage detection threshold voltage	DCDC output falling	2.1	2.25		V
$V_{HLDO\_OUT}$	High-side LDO output voltage	HLDO to HGND, 4 mA external load, $V_{DD} > 3.6\text{ V}$	3	3.2	3.4	V
$V_{HLDOUTV}$	High-side LDO output undervoltage detection threshold voltage	HLDO output falling	2.4	2.6		V
$I_H$	High-side supply current for auxiliary circuitry	$3\text{ V} \leq V_{DD} < 3.6\text{ V}$ , load connected from HLDO_OUT to HGND, non-switching			1	mA
		$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ , load connected from HLDO_OUT to HGND, non-switching			4.0	
$t_{AS}$	Analog settling time	VDD step to 3.0 V, to OUTP and OUTN valid, 0.1% settling		0.9	1.4	ms

- (1) The typical value includes one standard deviation ("sigma") at nominal operating conditions.
- (2) This parameter is input referred.
- (3) THD is the ratio of the rms sum of the amplitudes of first five higher harmonics to the amplitude of the fundamental.
- (4) Offset error temperature drift is calculated using the box method, as described by the following equation:  

$$TCV_{OS} = (V_{OS,MAX} - V_{OS,MIN}) / TempRange$$
where  $V_{OS,MAX}$  and  $V_{OS,MIN}$  refer to the maximum and minimum  $V_{OS}$  values measured within the temperature range ( $-40$  to  $125^\circ\text{C}$ ).
- (5) Gain error temperature drift is calculated using the box method, as described by the following equation:  

$$TCE_G (ppm) = ((E_{G,MAX} - E_{G,MIN}) / TempRange) \times 10^4$$
where  $E_{G,MAX}$  and  $E_{G,MIN}$  refer to the maximum and minimum  $E_G$  values (in %) measured within the temperature range ( $-40$  to  $125^\circ\text{C}$ ).

## 5.10 Switching Characteristics

over operating ambient temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_r$	Output signal rise time			1.3		$\mu\text{s}$
$t_f$	Output signal fall time			1.3		$\mu\text{s}$
	$V_{\text{INx}}$ to $V_{\text{OUTx}}$ signal delay (50% – 10%)	Unfiltered output		1	1.5	$\mu\text{s}$
	$V_{\text{INx}}$ to $V_{\text{OUTx}}$ signal delay (50% – 50%)	Unfiltered output		1.6	2.1	$\mu\text{s}$
	$V_{\text{INx}}$ to $V_{\text{OUTx}}$ signal delay (50% – 90%)	Unfiltered output		2.5	3	$\mu\text{s}$

## 5.11 Timing Diagram

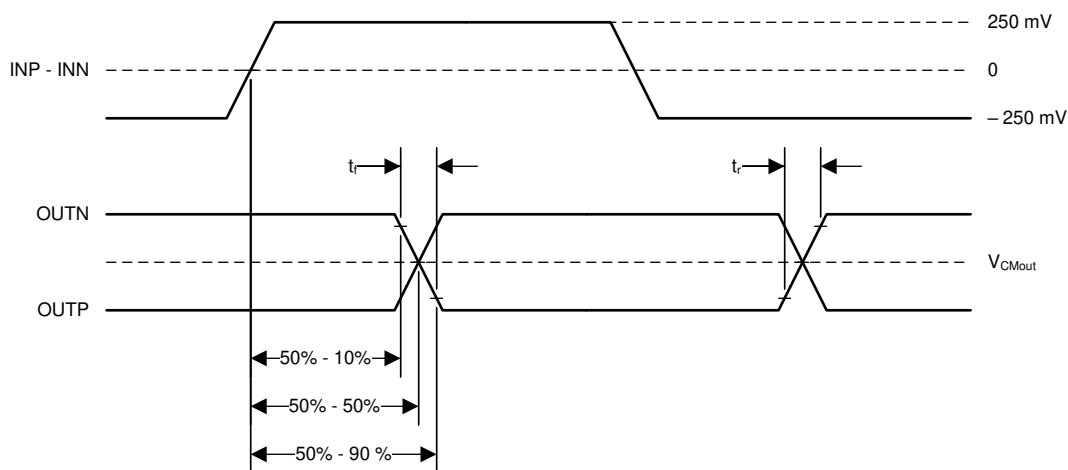


图 5-1. Rise, Fall, and Delay Time Waveforms

## 5.12 Insulation Characteristics Curves

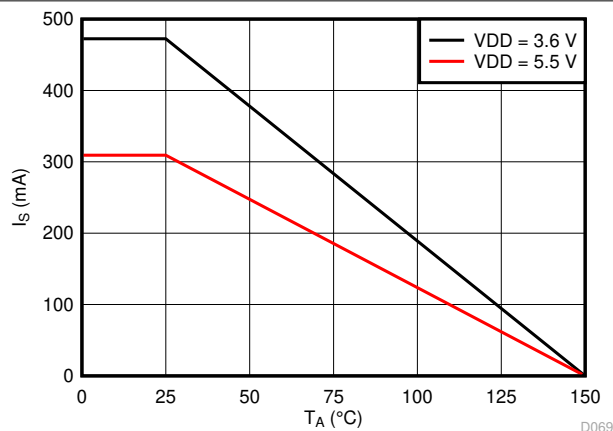


図 5-2. Thermal Derating Curve for Safety-Limiting Current per VDE

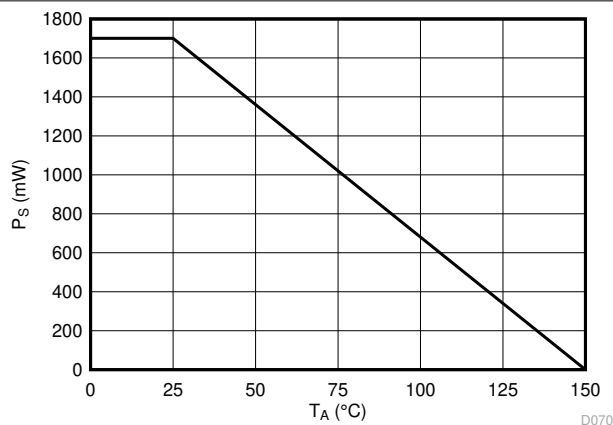
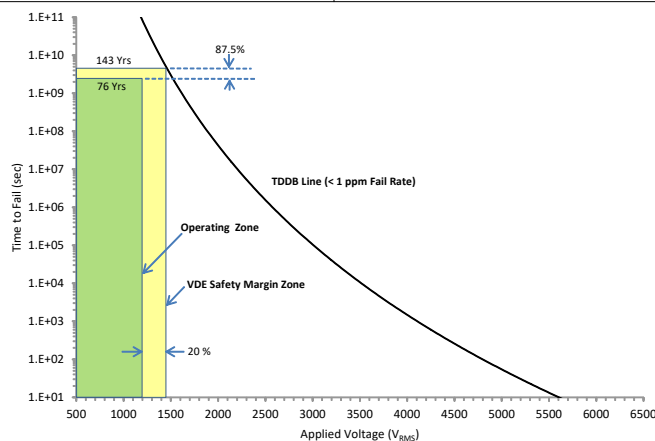


図 5-3. Thermal Derating Curve for Safety-Limiting Power per VDE



$T_A$  up to 150°C, stress-voltage frequency = 60 Hz,  
isolation working voltage = 1200  $V_{RMS}$ , operating lifetime = 76 years

図 5-4. Reinforced Isolation Capacitor Lifetime Projection

## 5.13 Typical Characteristics

at  $V_{DD} = 3.3\text{ V}$ ,  $INP = -250\text{ mV}$  to  $+250\text{ mV}$ ,  $INN = HGND = 0\text{ V}$ , and  $f_{IN} = 10\text{ kHz}$  (unless otherwise noted)

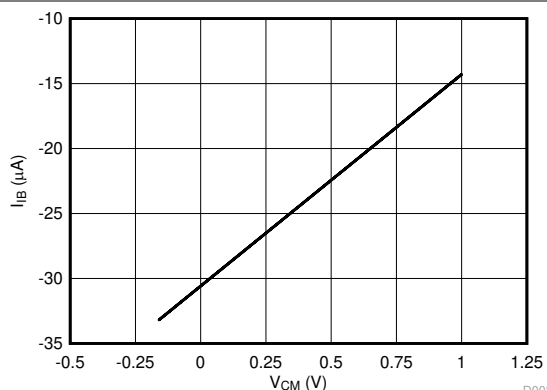


図 5-5. Input Bias Current vs Common-Mode Input Voltage

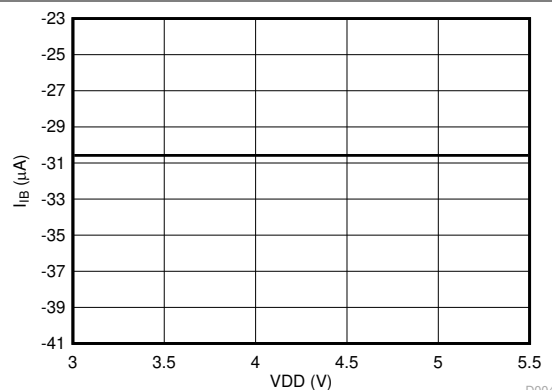


図 5-6. Input Bias Current vs Supply Voltage

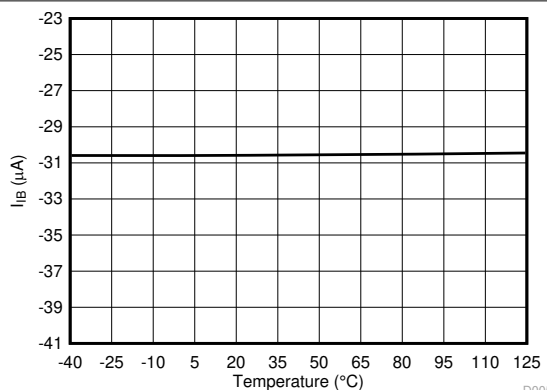


図 5-7. Input Bias Current vs Temperature

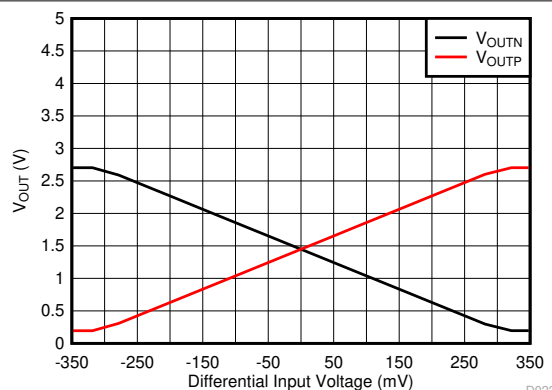


図 5-8. Output Voltage vs Input Voltage

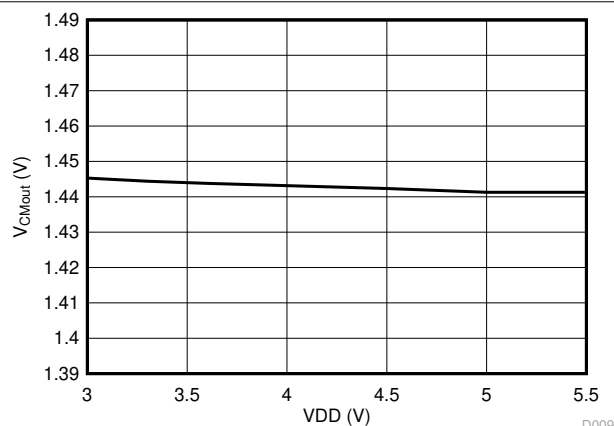


図 5-9. Output Common-Mode Voltage vs Supply Voltage

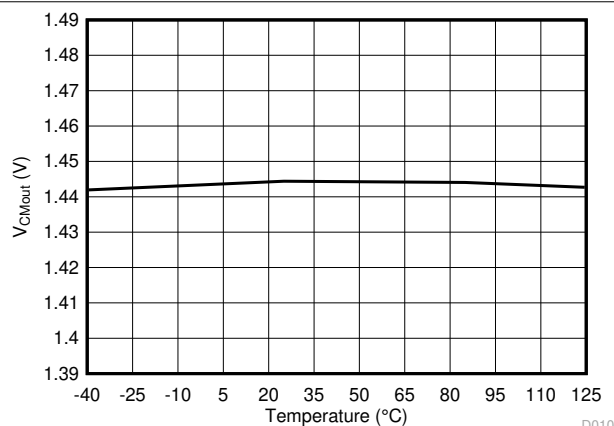


図 5-10. Output Common-Mode Voltage vs Temperature

## 5.13 Typical Characteristics (continued)

at  $V_{DD} = 3.3\text{ V}$ ,  $INP = -250\text{ mV}$  to  $+250\text{ mV}$ ,  $INN = HGND = 0\text{ V}$ , and  $f_{IN} = 10\text{ kHz}$  (unless otherwise noted)

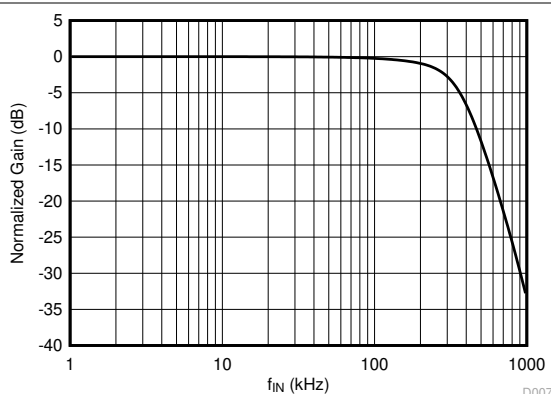


Figure 5-11. Normalized Gain vs Input Frequency

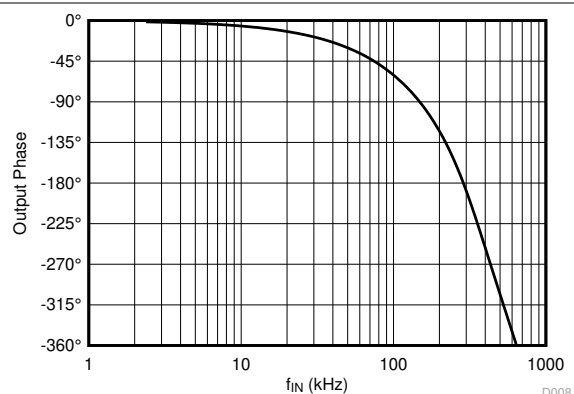


Figure 5-12. Output Phase vs Input Frequency

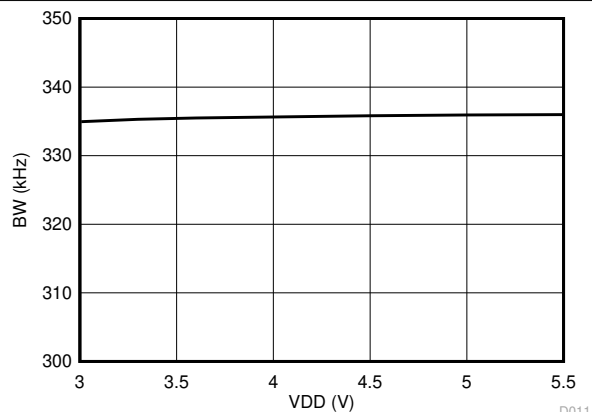


Figure 5-13. Output Bandwidth vs Supply Voltage

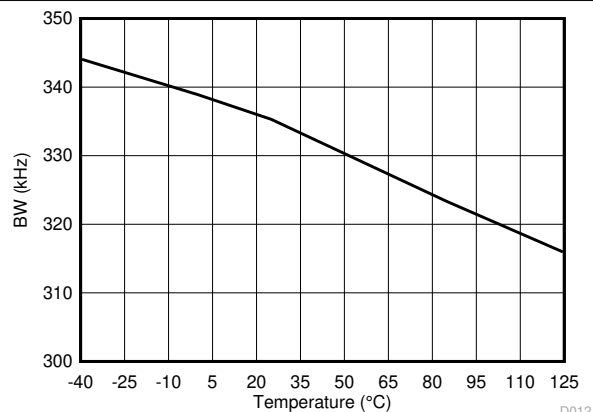


Figure 5-14. Output Bandwidth vs Temperature

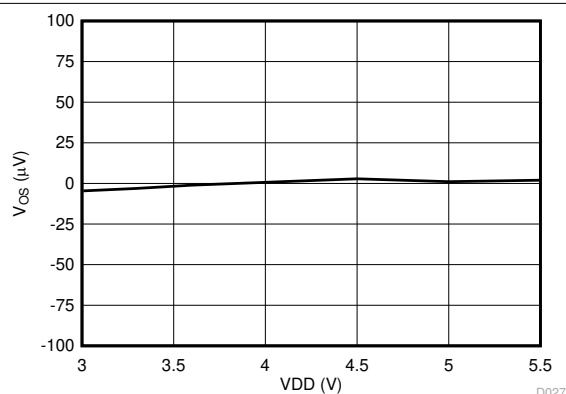


Figure 5-15. Input Offset Voltage vs Supply Voltage

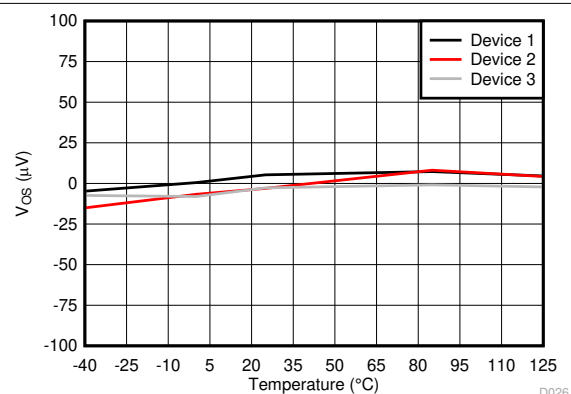


Figure 5-16. Input Offset Voltage vs Temperature

## 5.13 Typical Characteristics (continued)

at  $V_{DD} = 3.3\text{ V}$ ,  $INP = -250\text{ mV}$  to  $+250\text{ mV}$ ,  $INN = HGND = 0\text{ V}$ , and  $f_{IN} = 10\text{ kHz}$  (unless otherwise noted)

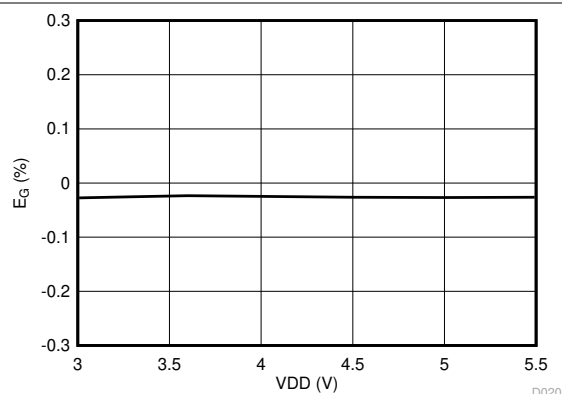


図 5-17. Gain Error vs Supply Voltage

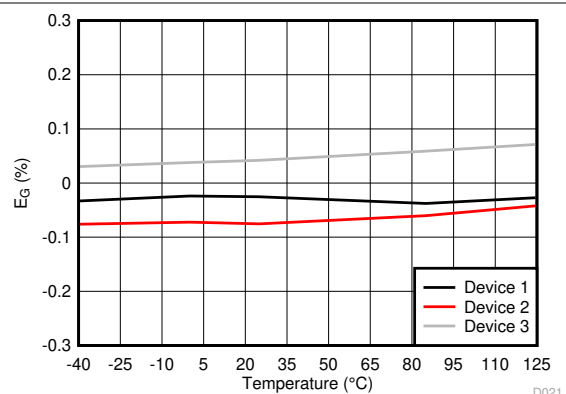


図 5-18. Gain Error vs Temperature

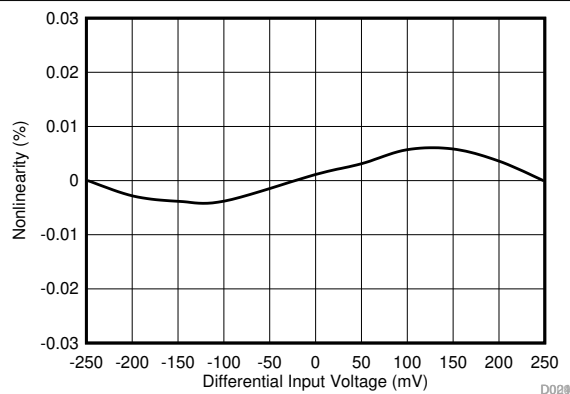


図 5-19. Nonlinearity vs Input Voltage

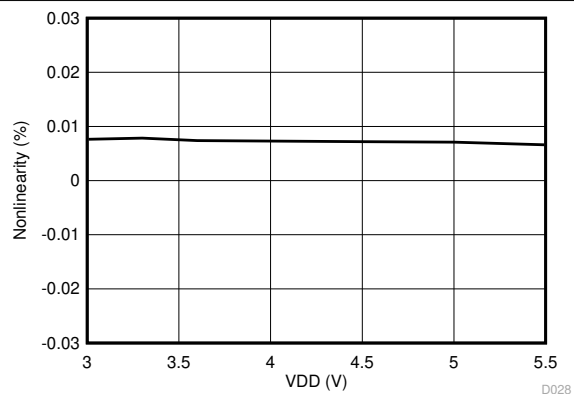


図 5-20. Nonlinearity vs Supply Voltage

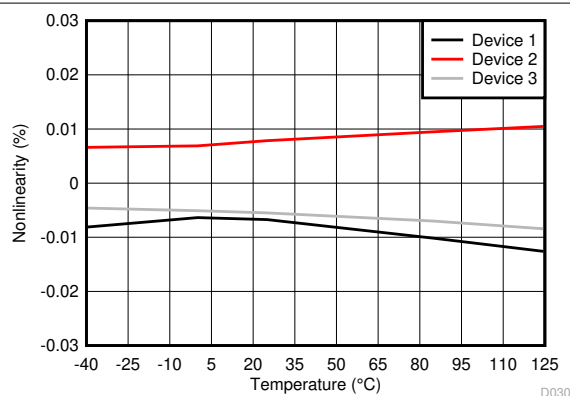


図 5-21. Nonlinearity vs Temperature

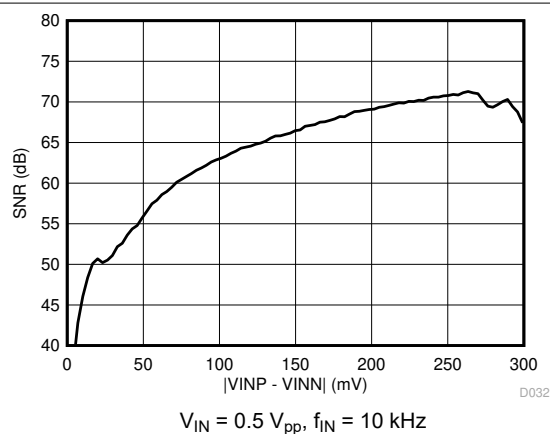


図 5-22. Signal-to-Noise Ratio vs Input Voltage

## 5.13 Typical Characteristics (continued)

at VDD = 3.3 V, INP = –250 mV to +250 mV, INN = HGND = 0 V, and  $f_{IN} = 10$  kHz (unless otherwise noted)

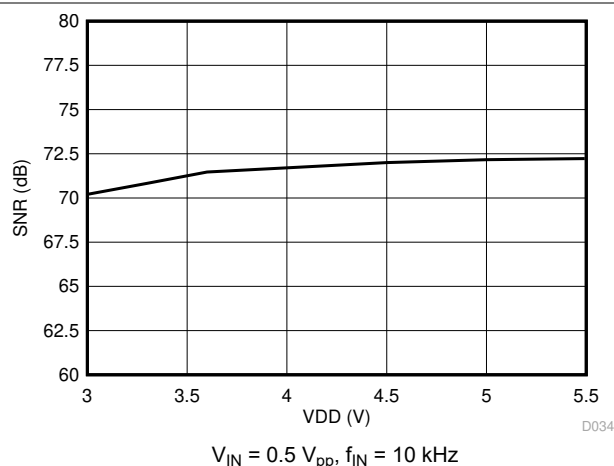


図 5-23. Signal-to-Noise Ratio vs Supply Voltage

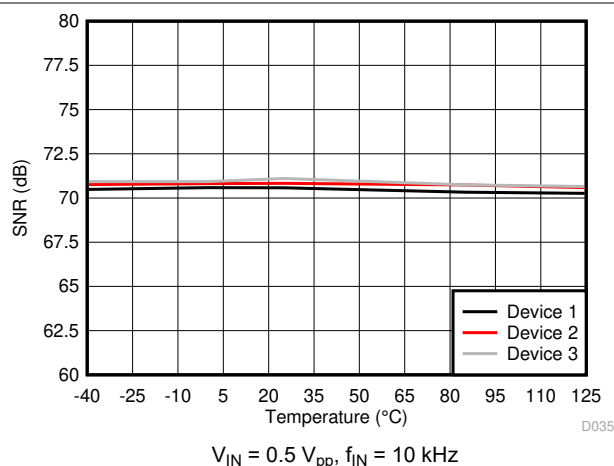


図 5-24. Signal-to-Noise Ratio vs Temperature

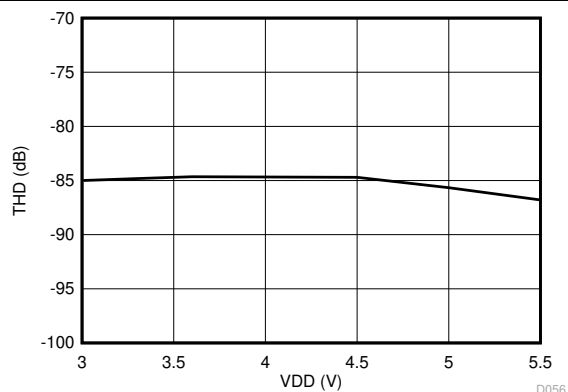


図 5-25. Total Harmonic Distortion vs Supply Voltage

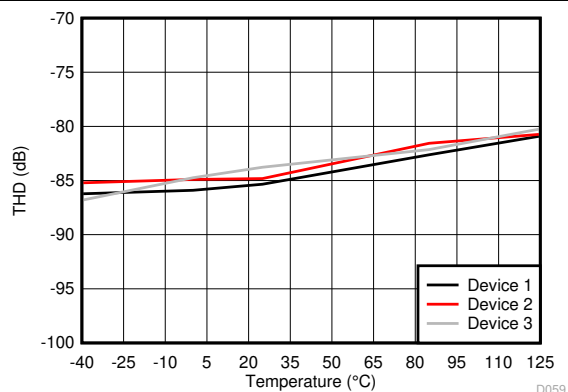


図 5-26. Total Harmonic Distortion vs Temperature

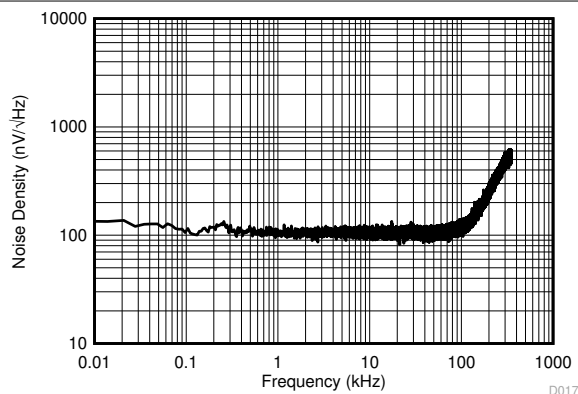


図 5-27. Input-Referred Noise Density vs Frequency

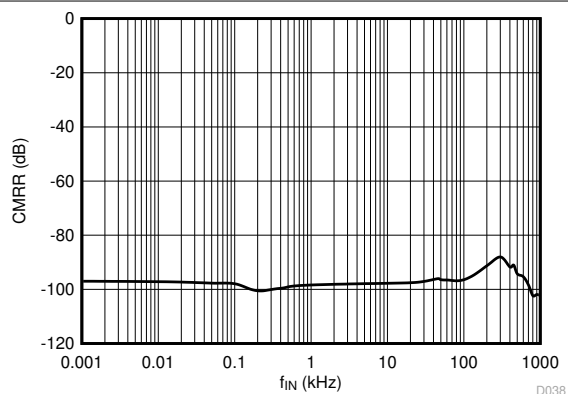


図 5-28. Common-Mode Rejection Ratio vs Input Frequency

## 5.13 Typical Characteristics (continued)

at VDD = 3.3 V, INP = –250 mV to +250 mV, INN = HGND = 0 V, and  $f_{IN} = 10$  kHz (unless otherwise noted)

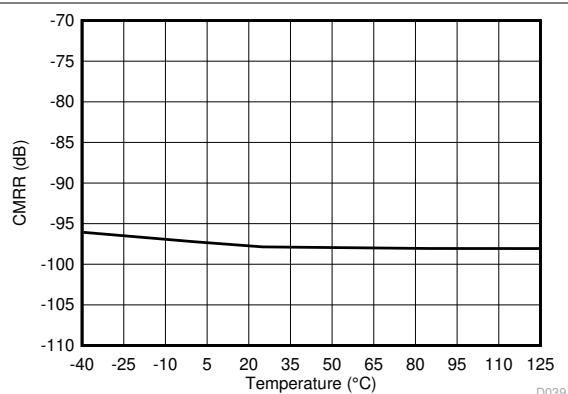


図 5-29. Common-Mode Rejection Ratio vs Temperature

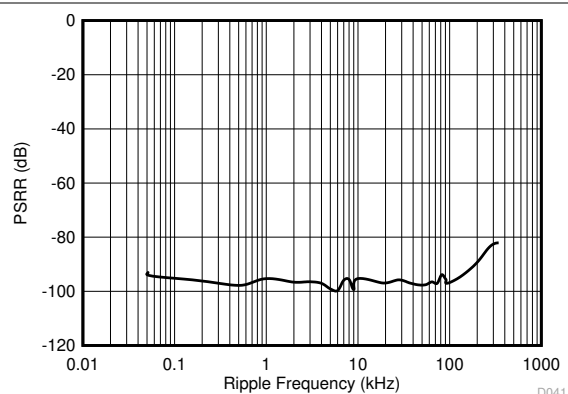


図 5-30. Power-Supply Rejection Ratio vs Ripple Frequency

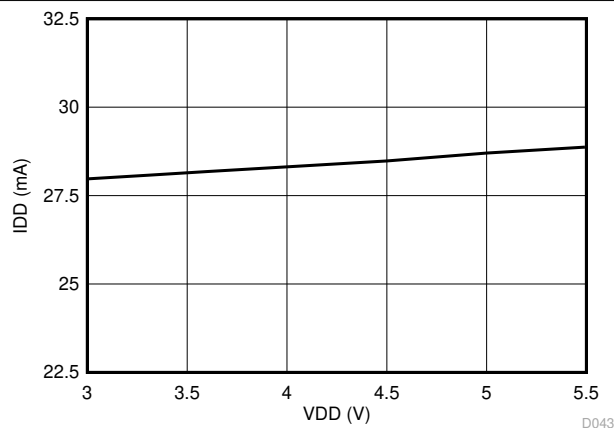


図 5-31. Supply Current vs Supply Voltage

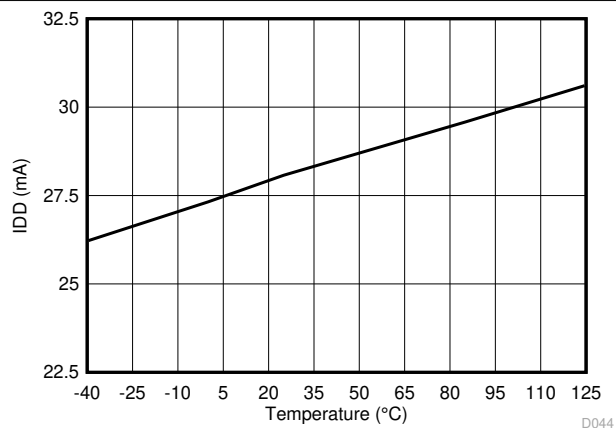


図 5-32. Supply Current vs Temperature

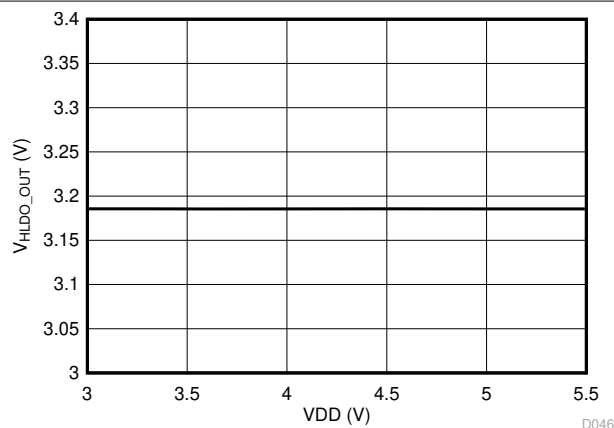


図 5-33. High-Side LDO Line Regulation

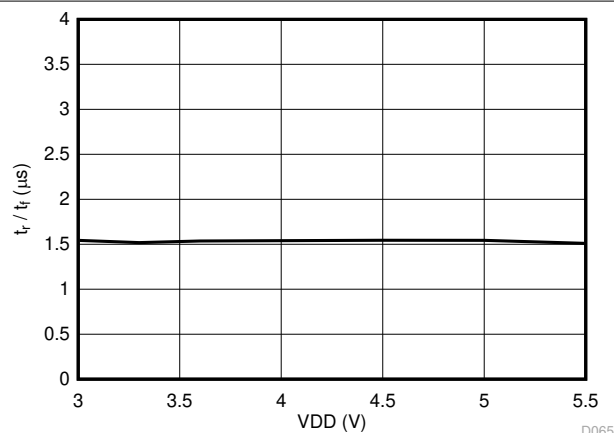


図 5-34. Output Rise and Fall time vs Supply Voltage



## 5.13 Typical Characteristics (continued)

at VDD = 3.3 V, INP = –250 mV to +250 mV, INN = HGND = 0 V, and  $f_{IN} = 10$  kHz (unless otherwise noted)

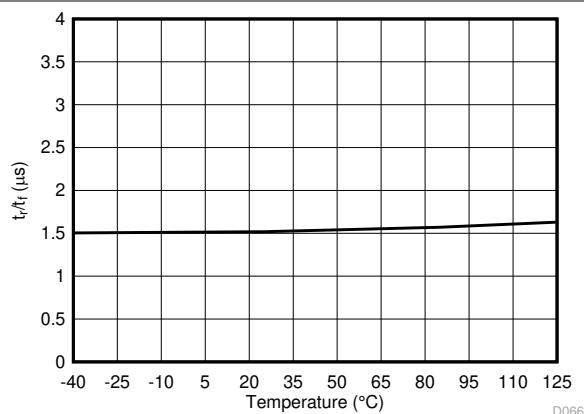


Figure 5-35. Output Rise and Fall Time vs Temperature

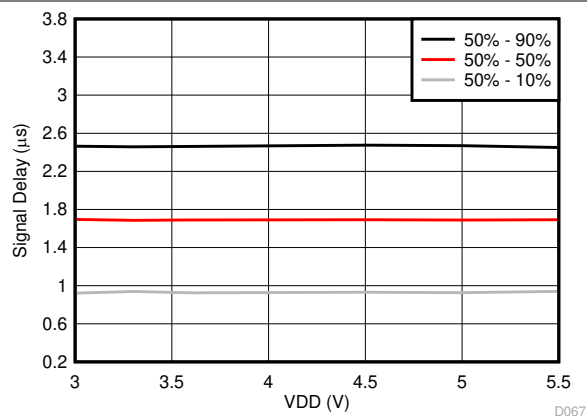


Figure 5-36. VIN to VOUT Signal Delay vs Supply Voltage

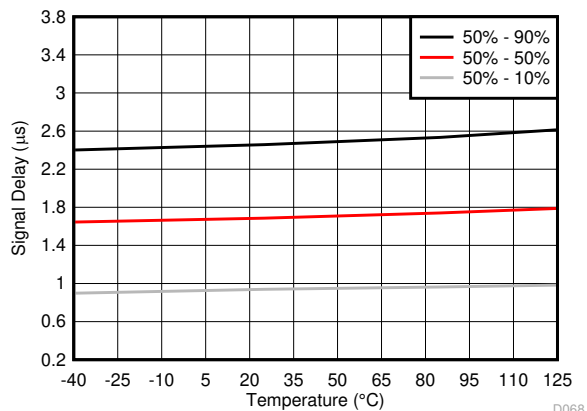


Figure 5-37. VIN to VOUT Signal Delay vs Temperature

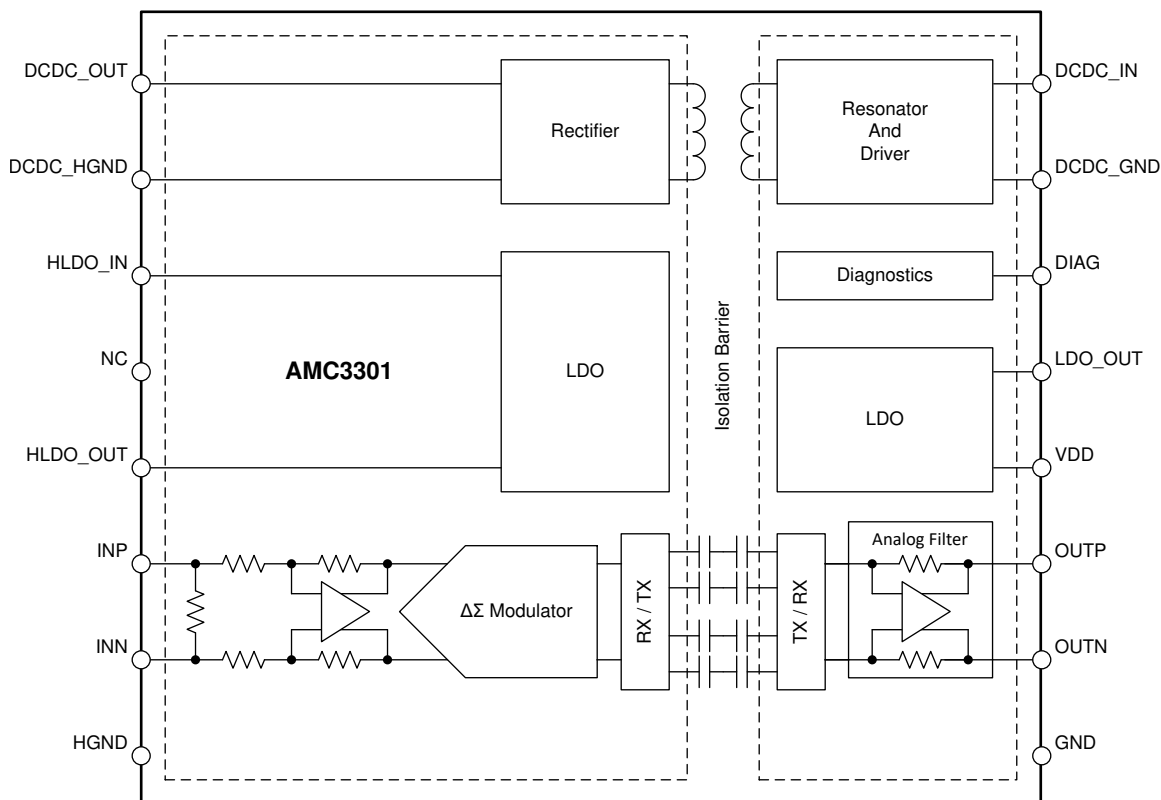
## 6 Detailed Description

### 6.1 Overview

The AMC3301 is a fully differential, precision, isolated amplifier with a fully integrated DC/DC converter that can supply the device from a single 3.3-V or 5-V voltage supply on the low-side. The input stage of the device consists of a fully differential amplifier that drives a second-order, delta-sigma ( $\Delta\Sigma$ ) modulator. The modulator uses an internal voltage reference and clock generator to convert the analog input signal to a digital bitstream. The drivers (termed *TX* in the [Functional Block Diagram](#)) transfer the output of the modulator across the isolation barrier that separates the high-side and low-side voltage domains. As shown in the *Functional Block Diagram*, the received bitstream and clock are synchronized and processed by a fourth-order analog filter on the low-side and presented as a differential output of the device

The signal path is isolated by a double capacitive silicon dioxide ( $\text{SiO}_2$ ) insulation barrier, whereas power isolation uses an on-chip transformer separated by a thin-film polymer as the insulating material.

### 6.2 Functional Block Diagram



### 6.3 Feature Description

#### 6.3.1 Analog Input

The differential amplifier input stage of the AMC3301 feeds a second-order, switched-capacitor, feed-forward  $\Delta\Sigma$  modulator. The gain of the differential amplifier is set by internal precision resistors with a differential input impedance of  $R_{IND}$ . The modulator converts the analog signal into a bitstream that is transferred across the isolation barrier, as described in the [Data Isolation Channel Signal Transmission](#) section.

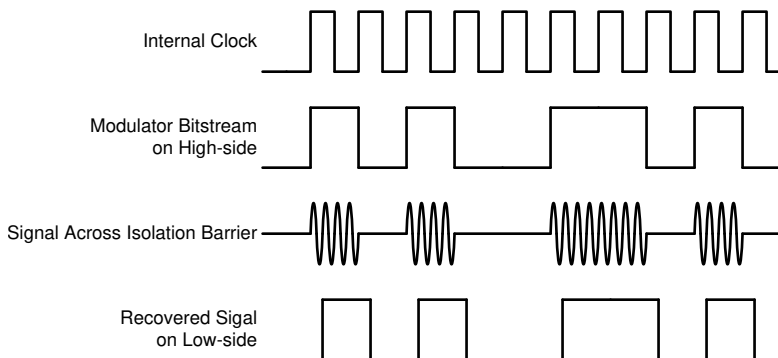
There are two restrictions on the analog input signals (INP and INN). First, if the input voltages  $V_{INP}$  or  $V_{INN}$  exceed the range specified in the [Absolute Maximum Ratings](#) table, the input current must be limited to the absolute maximum value, because the device input electrostatic discharge (ESD) diodes turn on. In addition, the linearity and parametric performance of the device are ensured only when the analog input voltage remains

within linear full-scale range ( $V_{FSR}$ ) and within the common-mode input voltage range ( $V_{CM}$ ) as specified in the [Recommended Operating Conditions](#) table.

### 6.3.2 Data Isolation Channel Signal Transmission

The AMC3301 uses an on-off keying (OOK) modulation scheme, as shown in [Figure 6-1](#), to transmit the modulator output bitstream across the capacitive SiO<sub>2</sub>-based isolation barrier. The transmit driver (TX) shown in the [Functional Block Diagram](#) transmits an internally generated, high-frequency carrier across the isolation barrier to represent a digital *one* and does not send a signal to represent a digital *zero*. The nominal frequency of the carrier used inside the AMC3301 is 480 MHz.

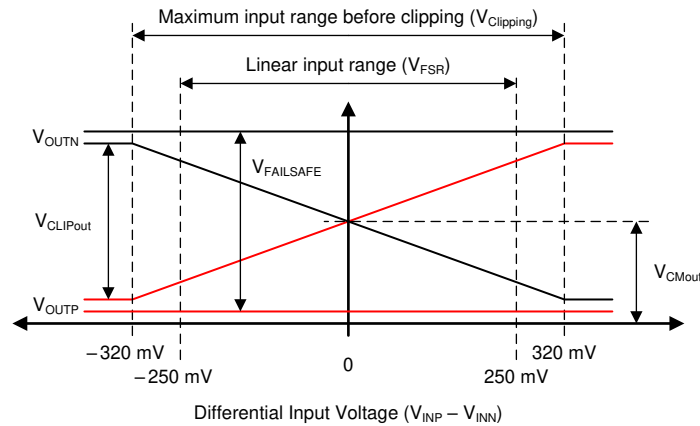
The receiver (RX) on the other side of the isolation barrier recovers and demodulates the signal and produces the output. The AMC3301 transmission channel is optimized to achieve the highest level of common-mode transient immunity (CMTI) and lowest level of radiated emissions caused by the high-frequency carrier and RX/TX buffer switching.



**Figure 6-1. OOK-Based Modulation Scheme**

### 6.3.3 Analog Output

The AMC3301 offers a differential analog output comprised of the OUTP and OUTN pins. For differential input voltages ( $V_{INP} - V_{INN}$ ) in the range from  $-250\text{ mV}$  to  $+250\text{ mV}$ , the device provides a linear response with a nominal gain of 8.2. For example, for a differential input voltage of  $250\text{ mV}$ , the differential output voltage ( $V_{OUTP} - V_{OUTN}$ ) is  $2.05\text{ V}$ . At zero input (INP shorted to INN), both pins output the same common-mode output voltage  $V_{CMout}$ , as specified in the [Electrical Characteristics](#) table. For absolute differential input voltages greater than  $250\text{ mV}$  but less than  $320\text{ mV}$ , the differential output voltage continues to increase in magnitude but with reduced linearity performance. The outputs saturate at a differential output voltage of  $V_{CLIPout}$  as shown in [Figure 6-2](#) if the differential input voltage exceeds the  $V_{Clipping}$  value.



**Figure 6-2. Output Behavior of the AMC3301**

The AMC3301 provides a fail-safe output that simplifies diagnostics on system level. [Figure 6-2](#) shows the fail-safe mode, in which the AMC3301 outputs a negative differential output voltage that does not occur under normal operating conditions. The fail-safe output is active in two cases:

- The low-side does not receive data from the high-side (for example, because of a loss of power on the high side).
- The high-side DC/DC output voltage (DCDC\_OUT) or the high-side LDO output voltage (HLDO\_OUT) drop below their respective undervoltage detection thresholds (brown-out).

Use the maximum  $V_{FAILSAFE}$  voltage specified in the [Electrical Characteristics](#) table as a reference value for the fail-safe detection on the system level.

### 6.3.4 Isolated DC/DC Converter

The AMC3301 offers a fully integrated isolated DC/DC converter that includes the following components as illustrated in the [Functional Block Diagram](#):

- Low-dropout regulator (LDO) on the low-side to stabilize the supply voltage VDD that drives the low-side of the converter. This circuit does not output a constant voltage and is not intended for driving any external load.
- Low-side full-bridge inverter and drivers
- Laminate-based, air-core transformer for high-immunity to magnetic fields
- High-side full-bridge rectifier
- High-side LDO to stabilize the output voltage of the DC/DC converter for high analog performance of the signal path. The high-side LDO outputs a constant voltage and can provide a limited amount of current to power external circuitry.

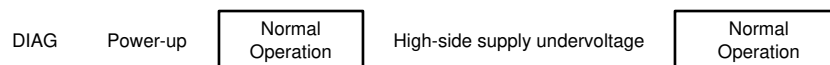
The DC/DC converter uses a spread-spectrum clock generation technique to reduce the spectral density of the electromagnetic radiation. The resonator frequency is synchronized to the operation of the  $\Delta\Sigma$  modulator to minimize the interference with data transmission and support the high analog performance of the device.

The architecture of the DC/DC converter is optimized to drive the high-side circuitry of the AMC3301 and can source up to  $I_H$  of additional DC current for an optional auxiliary circuit such as an active filter, preamplifier, or comparator.  $I_H$  is specified in the [Electrical Characteristics](#) table as a DC, non-switching current.

### 6.3.5 Diagnostic Output

The open-drain DIAG pin can be monitored to confirm the device is operational and the output voltage is valid. As shown in [Figure 6-3](#), during power-up, the DIAG pin is actively held low until the high-side supply is in regulation and the device operates properly. During normal operation, the DIAG pin is in high-impedance (Hi-Z) state and is pulled high through an external pullup resistor. The DIAG pin is actively pulled low if:

- The low-side does not receive data from the high-side (for example, because of a loss of power on the high side). In this case, the amplifier outputs are driven to the  $V_{\text{FAILSAFE}}$  value that is shown in [Figure 6-2](#).
- The high-side DC/DC output voltage (DCDC\_OUT) or the high-side LDO output voltage (HLDO\_OUT) drop below their respective undervoltage detection thresholds (brown-out). In this case, the low-side may still receive data from the high-side but the data may not be valid. The amplifier outputs are driven to the  $V_{\text{FAILSAFE}}$  value that is shown in [Figure 6-2](#).



**Figure 6-3. DIAG Output Under Different Operating Conditions**

During normal operation, the DIAG pin is in a high-impedance state. Connect the DIAG pin to a pullup resistor or leave open if not used.

## 6.4 Device Functional Modes

The AMC3301 is operational when the power supply VDD is applied, as specified in the [Recommended Operating Conditions](#) table.

## 7 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 7.1 Application Information

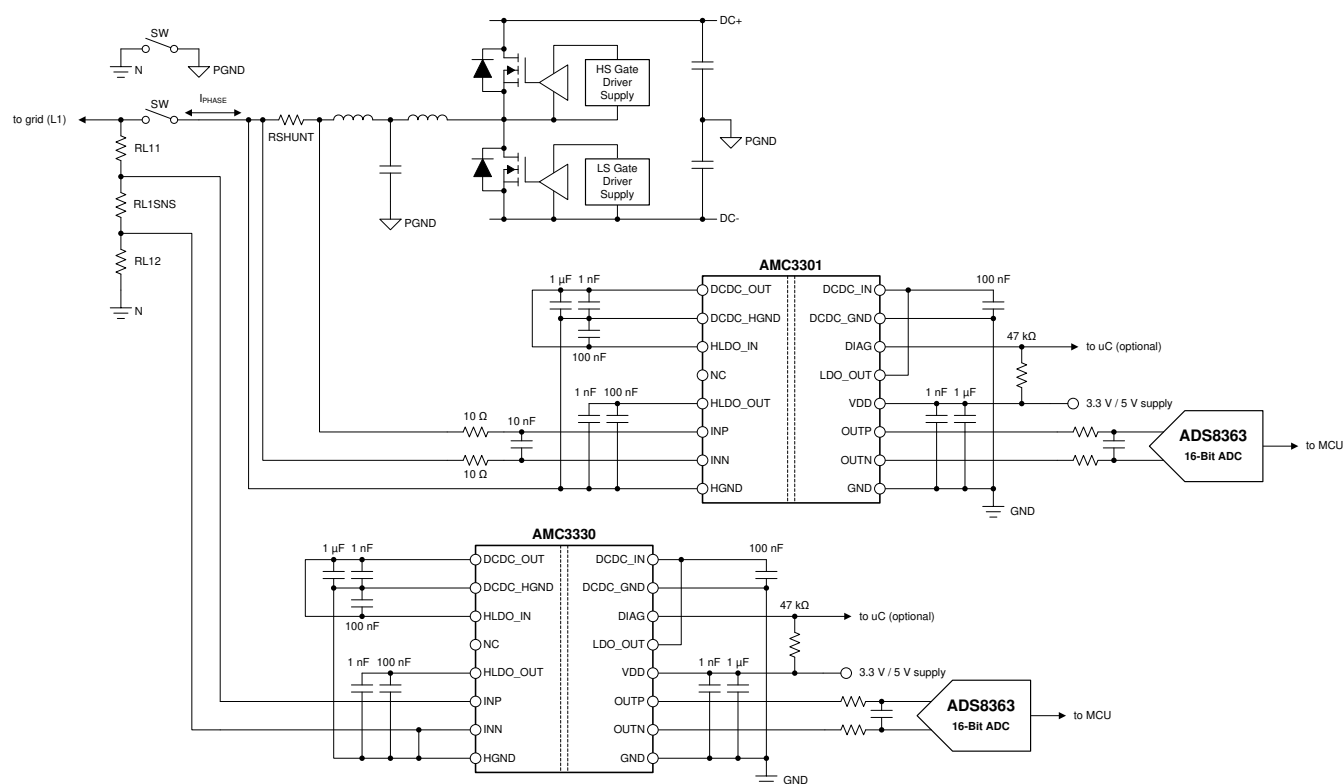
The low input voltage range, low nonlinearity, and low temperature drift make the AMC3301 a high-performance solution for industrial applications where shunt-based current sensing with high common-mode voltage levels is required.

### 7.2 Typical Application

The AMC3301 is ideally suited for shunt-based current sensing applications where accurate current monitoring is required in the presence of high common-mode voltages. The AMC3301 integrates an isolated power supply for the high-voltage side and therefore makes the device particularly easy to use in applications that do not have a high-side supply readily available or where a high-side supply is referenced to a different ground potential than the signal to be measured.

☒ **7-1** shows a simplified schematic of the AMC3301 in a solar inverter where the phase current is measured on the grid-side of an LCL filter. Although the system offers a supply for the high-side gate driver, there is a large common-mode voltage between the gate driver supply ground reference and the shunt resistor on the other side of the LCL filter. Therefore, the gate driver supply is not suitable for powering the high-side of an isolated amplifier that measures the voltage across the shunt. The integrated isolated power supply of the AMC3301 solves that problem and enables current sensing at locations that is optimal for the system.

The diagram also shows the [AMC3330](#) being used for sensing the AC output voltage.



## ☒ 7-1. The AMC3301 in a Solar Inverter Application



### 7.2.1 Design Requirements

表 7-1 lists the parameters for this typical application.

### 表 7-1. Design Requirements

PARAMETER	VALUE
Supply voltage	3.3 V or 5 V
Voltage drop across the shunt for a linear response ( $V_{SHUNT}$ )	$\pm 250$ mV (maximum)

### 7.2.2 Detailed Design Procedure

The AMC3301 requires a single 3.3-V or 5-V supply on its low-side. The high-side supply is internally generated by an integrated DC/DC converter as explained in the [Isolated DC/DC Converter](#) section.

The ground reference (HGND) is derived from the terminal of the shunt resistor that is connected to the negative input of the AMC3301 (INN). If a four-pin shunt is used, the inputs of the AMC3301 are connected to the inner leads and HGND is connected to one of the outer shunt leads. To minimize offset and improve accuracy, set the ground connection to a separate trace that connects directly to the shunt resistor rather than shorting HGND to INN directly at the input to the device. See the [Layout](#) section for more details.

### 7.2.2.1 Shunt Resistor Sizing

Use Ohm's Law to calculate the voltage drop across the shunt resistor ( $V_{SHUNT}$ ) for the desired measured current:  $V_{SHUNT} = I \times R_{SHUNT}$ .

Consider the following two restrictions to choose the proper value of the shunt resistor,  $R_{SHUNT}$ :

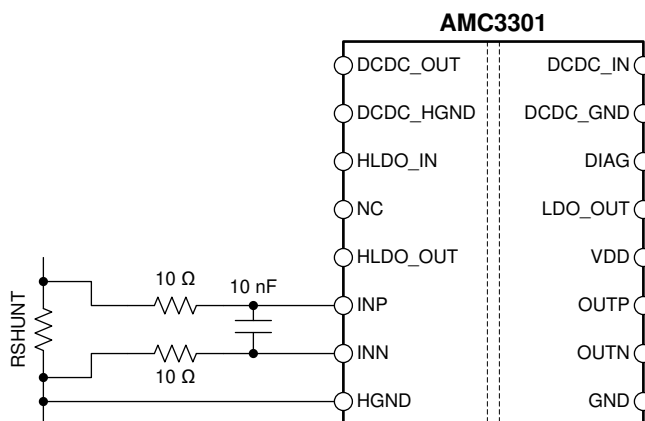
- The voltage drop caused by the nominal current range must not exceed the recommended differential input voltage range:  $|V_{SHUNT}| \leq |V_{FSR}|$
- The voltage drop caused by the maximum allowed overcurrent must not exceed the input voltage that causes a clipping output:  $|V_{SHUNT}| \leq |V_{Clipping}|$

#### 7.2.2.2 Input Filter Design

TI recommends placing an RC filter in front of the isolated amplifier to improve signal-to-noise performance of the signal path. Design the input filter such that:

- The cutoff frequency of the filter is at least one order of magnitude lower than the sampling frequency (20 MHz) of the  $\Delta\Sigma$  modulator
- The input bias current does not generate significant voltage drop across the DC impedance of the input filter
- The impedances measured from the analog inputs are equal

For most applications, the structure shown in  7-2 achieves excellent performance.



### 7-2. Differential Input Filter

### 7.2.2.3 Differential to Single-Ended Output Conversion

Figure 7-3 shows an example of a TLV6001 based signal conversion and filter circuit for systems using single-ended-input ADCs to convert the analog output voltage into digital. With  $R1 = R2 = R3 = R4$ , the output voltage equals  $(V_{OUTP} - V_{OUTN}) + V_{REF}$ . Tailor the bandwidth of this filter stage to the bandwidth requirement of the system. For most applications,  $R1 = R2 = R3 = R4 = 3.3 \text{ k}\Omega$  and  $C1 = C2 = 330 \text{ pF}$  yields good performance.

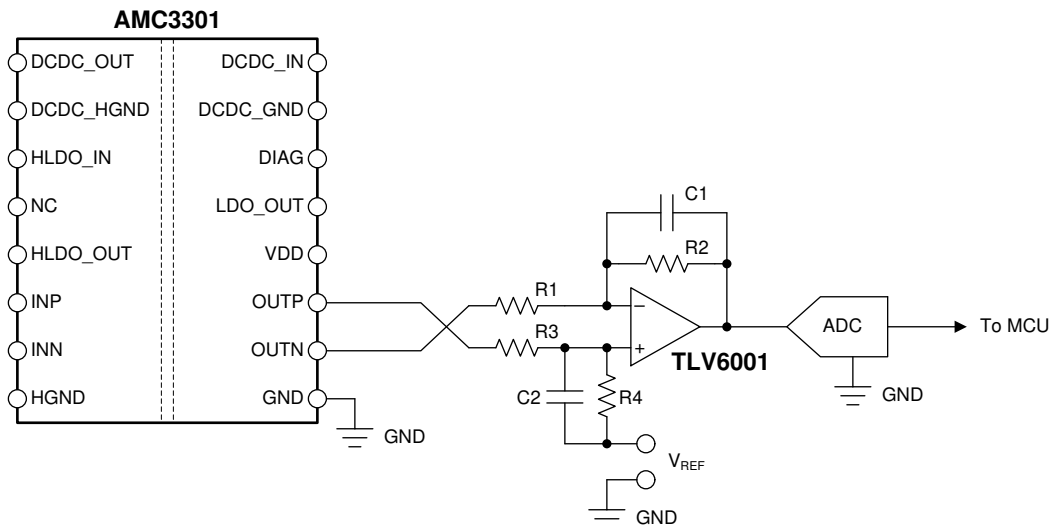


Figure 7-3. Connecting the AMC3301 Output to a Single-Ended Input ADC

For more information on the general procedure to design the filtering and driving stages of successive-approximation-register (SAR) ADCs, see the [18-Bit, 1MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise reference guide](#) and [18-Bit Data Acquisition Block \(DAQ\) Optimized for Lowest Power reference guide](#), available for download at [www.ti.com](http://www.ti.com).

### 7.2.3 Application Curve

In frequency inverter applications, the power switches must be protected in case of an overcurrent condition. To allow for fast powering off of the system, a low delay caused by the isolated amplifier is required. Figure 7-4 shows the typical full-scale step response of the AMC3301. Consider the delay of the required window comparator and the MCU to calculate the overall response time of the system.

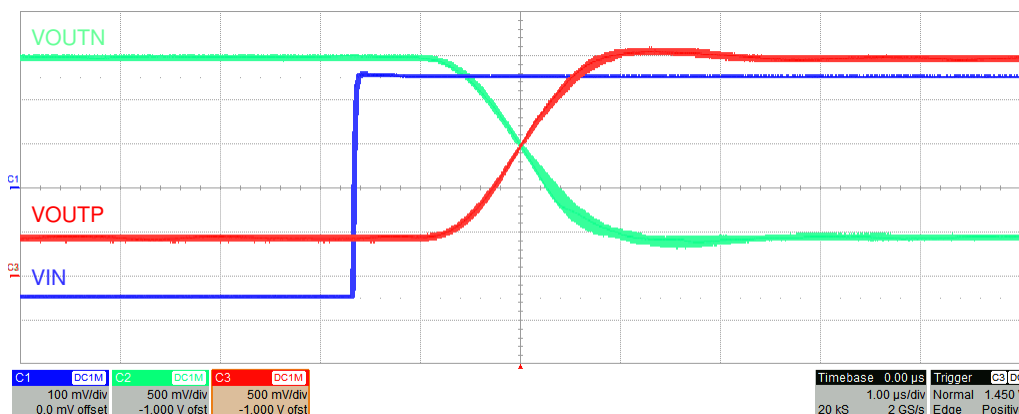


Figure 7-4. Step Response of the AMC3301

## 7.3 Best Design Practices

Do not leave the analog inputs INP and INN of the AMC3301 unconnected (floating) when the device is powered up. If the device inputs are left floating, the input bias current may drive the inputs to a positive value that exceeds the operating common-mode input voltage and the output of the device is undetermined.

Connect the negative input (INN) to the high-side ground (HGND), either by a hard short or through a resistive path. A DC current path between INN and HGND is required to define the input common-mode voltage. Take care not to exceed the input common-mode range as specified in the [Recommended Operating Conditions](#) table. For best accuracy, route the ground connection as a separate trace that connects directly to the shunt resistor rather than shorting AGND to INN directly at the input to the device. See the [Layout](#) section for more details.

The high-side LDO can source a limited amount of current ( $I_H$ ) to power external circuitry. Take care not to overload the high-side LDO.

The low-side LDO does not output a constant voltage and is not intended for powering any external circuitry. Do not connect any external load to the LDO\_OUT pin.

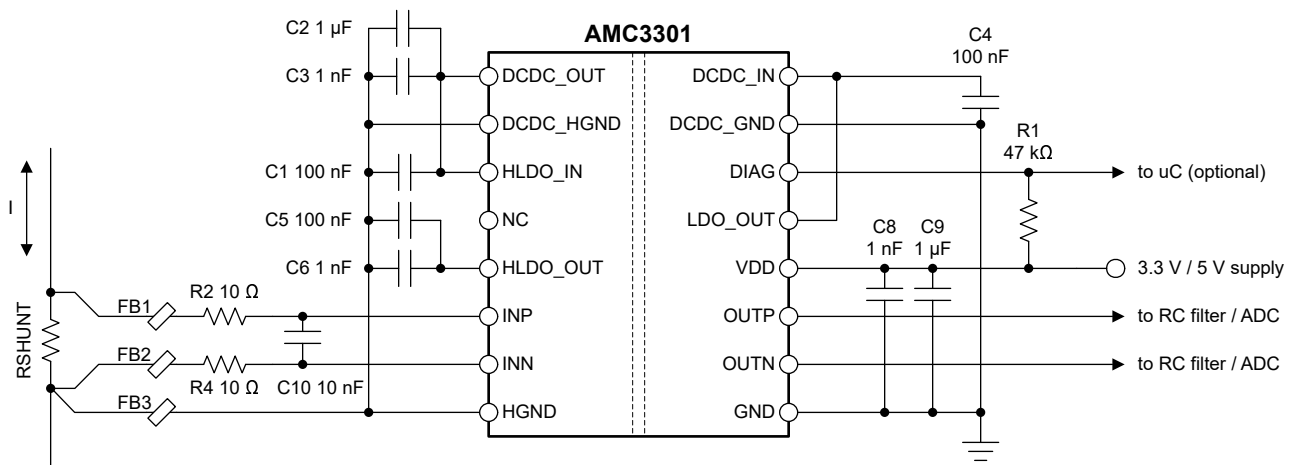
## 7.4 Power Supply Recommendations

The AMC3301 is powered from the low-side power supply (VDD) with a nominal value of 3.3 V or 5 V. TI recommends a low-ESR decoupling capacitor of 1 nF (C8 in [Figure 7-5](#)) placed as close as possible to the VDD pin, followed by a 1- $\mu$ F capacitor (C9) to filter this power-supply path.

The low-side of the DC/DC converter is decoupled with a low-ESR 100-nF capacitor (C4) positioned close to the device between the DCDC\_IN and DCDC\_GND pins. Use a 1- $\mu$ F capacitor (C2) to decouple the high side in addition to a low-ESR, 1-nF capacitor (C3) placed as close as possible to the device and connected to the DCDC\_OUT and DCDC\_HGND pins.

For the high-side LDO, use low-ESR capacitors of 1 nF (C6), placed as close as possible to the AMC3301, followed by a 100-nF decoupling capacitor (C5).

The ground reference for the high-side (HGND) is derived from the terminal of the shunt resistor which is connected to the negative input (INN) of the device. For best DC accuracy, use a separate trace to make this connection instead of shorting HGND to INN directly at the device input. The high-side DC/DC ground terminal (DCDC\_HGND) is shorted to HGND directly at the device pins.



**図 7-5. Decoupling the AMC3301**

Capacitors must provide adequate *effective* capacitance under the applicable DC bias conditions they experience in the application. Multilayer ceramic capacitors (MLCC) typically exhibit only a fraction of their nominal capacitance under real-world conditions and this factor must be taken into consideration when selecting

these capacitors. This problem is especially acute in low-profile capacitors, in which the dielectric field strength is higher than in taller components. Reputable capacitor manufacturers provide capacitance versus DC bias curves that greatly simplify component selection.

The [Best Practices to Attenuate AMC3301 Family Radiated Emissions EMI application note](#) is available for download at [www.ti.com](http://www.ti.com).

表 7-2 lists components suitable for use with the AMC3301. This list is not exhaustive. Other components may exist that are equally suitable (or better), however these listed components have been validated during the development of the AMC3301.

**表 7-2. Recommended External Components**

DESCRIPTION		PART NUMBER	MANUFACTURER	SIZE (EIA, L x W)
VDD				
C8	1 nF ± 10%, X7R, 50 V	12065C102KAT2A	AVX	1206, 3.2 mm x 1.6 mm
C9	1 µF ± 10%, X7R, 25 V	12063C105KAT2A	AVX	1206, 3.2 mm x 1.6 mm
DC/DC CONVERTER				
C4	100 nF ± 10%, X7R, 50 V	C0603C104K5RACAUTO	Kemet	0603, 1.6 mm x 0.8 mm
C3	1 nF ± 10%, X7R, 50 V	C0603C102K5RACTU	Kemet	0603, 1.6 mm x 0.8 mm
C2	1 µF ± 10%, X7R, 25 V	CGA3E1X7R1E105K080AC	TDK	0603, 1.6 mm x 0.8 mm
HLDO				
C1	100 nF ± 10%, X7R, 50 V	C0603C104K5RACAUTO	Kemet	0603, 1.6 mm x 0.8 mm
C5	100 nF ± 5%, NP0, 50 V	C3216NP01H104J160AA	TDK	1206, 3.2 mm x 1.6 mm
C6	1 nF ± 10%, X7R, 50 V	12065C102KAT2A	AVX	1206, 3.2 mm x 1.6 mm
FERRITE BEADS				
FB1, FB2, FB3	Ferrite bead <sup>(1)</sup>	74269244182	Würth Elektronik	0402, 1.0mm × 0.5mm
		BLM15HD182SH1	Murata	0402, 1.0mm × 0.5mm
		BKH1005LM182-T	Taiyo Yuden	0402, 1.0mm × 0.5mm

(1) No ferrite beads are used for parametric validation.

## 7.5 Layout

### 7.5.1 Layout Guidelines

Figure 7-6 shows a layout recommendation with the critical placement of the decoupling capacitors. The same component reference designators are used as in the [Power Supply Recommendations](#) section. Decoupling capacitors are placed as close as possible to the AMC3301 supply pins. For best performance, place the shunt resistor close to the INP and INN inputs of the AMC3301 and keep the layout of both connections symmetrical.

To avoid causing errors in the measurement by the input bias currents of the AMC3301, connect the high-side ground pin (HGND) to the INN-side of the shunt resistor. Use a separate trace in the layout to make this connection to maintain equal currents in the INN and INP traces.

### 7.5.2 Layout Example

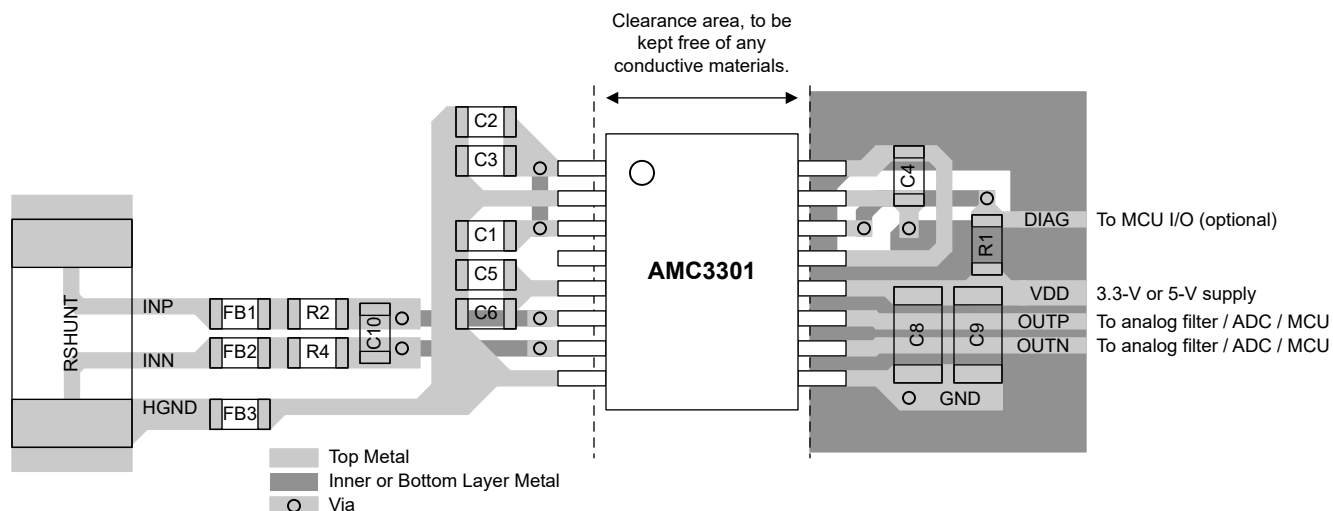


Figure 7-6. Recommended Layout of the AMC3301

## 8 Device and Documentation Support

### 8.1 Device Support

#### 8.1.1 Device Nomenclature

Texas Instruments, [Isolation Glossary](#)

### 8.2 Documentation Support

#### 8.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [ISO72x Digital Isolator Magnetic-Field Immunity](#) application report
- Texas Instruments, [AMC3330 Precision,  \$\pm 1\$ -V Input, Reinforced Isolated Amplifier](#) data sheet
- Texas Instruments, [TLV600x Low-Power, Rail-to-Rail In/Out, 1-MHz Operational Amplifier for Cost-Sensitive Systems](#) data sheet
- Texas Instruments, [18-Bit, 1-MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise](#) reference guide
- Texas Instruments, [18-Bit, 1-MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Power](#) reference guide

### 8.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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この用語集には、用語や略語の一覧および定義が記載されています。

## 9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

<b>Changes from Revision B (May 2021) to Revision C (May 2025)</b>	<b>Page</b>
ドキュメント全体を通して強化絶縁安全関連認定を「VDE V 0884-11」から「DIN EN IEC 60747-17 (VDE 0884-17)」に変更.....	1
Added analog output capacitive and resistive drive capability specification.....	4
Added DIGITAL OUTPUT (DIAG) specification.....	4
Updated Barrier capacitance specification from 3.5 pF to 4.5 pF.....	6
Changed isolation standard from DIN VDE V 0884-11 (VDE V 0884-11) to DIN EN IEC 60747-17 (VDE 0884-17) and updated the Insulation Specifications and Safety-Related Certifications tables accordingly.....	7
Added DIGITAL OUTPUT (DIAG) electrical specifications.....	8
Added VDD <sub>UV</sub> and VDD <sub>POR</sub> specifications.....	8
Added IH specification for 3.6 V ≤ VDD ≤ 5.5 V.....	8
Changed HLDO_OUT pin to LDO_OUT pin in Best Design Practices section.....	27

<b>Changes from Revision A (July 2020) to Revision B (May 2021)</b>	<b>Page</b>
「特長」セクションを変更。「小さな DC 誤差」の箇条書き項目の「オフセット電圧」と「オフセットドリフト」の箇条書き副項目を変更。箇条書き項目の順序を変更。最後の箇条書き項目を追加。.....	1
「アプリケーション」セクションの対象アプリケーションを絶縁型電圧センシングから絶縁型シャント・ベース電流センシングに変更.....	1
Changed Pin Configuration and Functions section.....	3
Changed Absolute Maximum Ratings: changed max for DIAG pin from 5.5 V to 6.5 V.....	4
Changed overvoltage category for rated mains voltage ≤ 600 V from I-IV to I-III and for rated mains voltage ≤ 1000 V from I-III to I-II.....	6
Changed output bandwidth (BW) (min) from 250 kHz to 290 kHz.....	8
Changed Typical Characteristics section. Removed histograms, editorial changes.....	12
Changed Functional Block Diagram figure.....	18
Changed Data Isolation Channel Signal Transmission section.....	20
Changed Analog Output section.....	21
Changed Diagnostic Output section: added DIAG Output Under Different Operating Conditions figure.....	22
Changed Typical Application section.....	23
Changed Input Filter Design section: changed Differential Input Filter figure.....	25
Added Differential to Single-Ended Output Conversion section.....	26
Changed Step Response of the AMC3301 figure.....	26
Changed Power Supply Recommendations section: changed nominal value in the first sentence from 3.3 V (or 5 V) ± 10 V to 3.3 V or 5 V, changed primary-side to low-side, secondary-side to high-side, and Decoupling the AMC3301 figure.....	27
Changed Recommended Layout of the AMC3301 figure.....	29

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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## PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">AMC3301DWE</a>	Active	Production	SOIC (DWE)   16	40   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWE.A	Active	Production	SOIC (DWE)   16	40   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWE.B	Active	Production	SOIC (DWE)   16	40   TUBE	-	Call TI	Call TI	-40 to 125	
AMC3301DWE.G4	Active	Production	SOIC (DWE)   16	40   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWE.G4.A	Active	Production	SOIC (DWE)   16	40   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWE.G4.B	Active	Production	SOIC (DWE)   16	40   TUBE	-	Call TI	Call TI	-40 to 125	
<a href="#">AMC3301DWER</a>	Active	Production	SOIC (DWE)   16	2000   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWER.A	Active	Production	SOIC (DWE)   16	2000   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC3301
AMC3301DWER.B	Active	Production	SOIC (DWE)   16	2000   LARGE T&R	-	Call TI	Call TI	-40 to 125	

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

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<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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**OTHER QUALIFIED VERSIONS OF AMC3301 :**

- Automotive : [AMC3301-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
AMC3301DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
AMC3301DWER	SOIC	DWE	16	2000	350.0	350.0	43.0

## TUBE



\*All dimensions are nominal

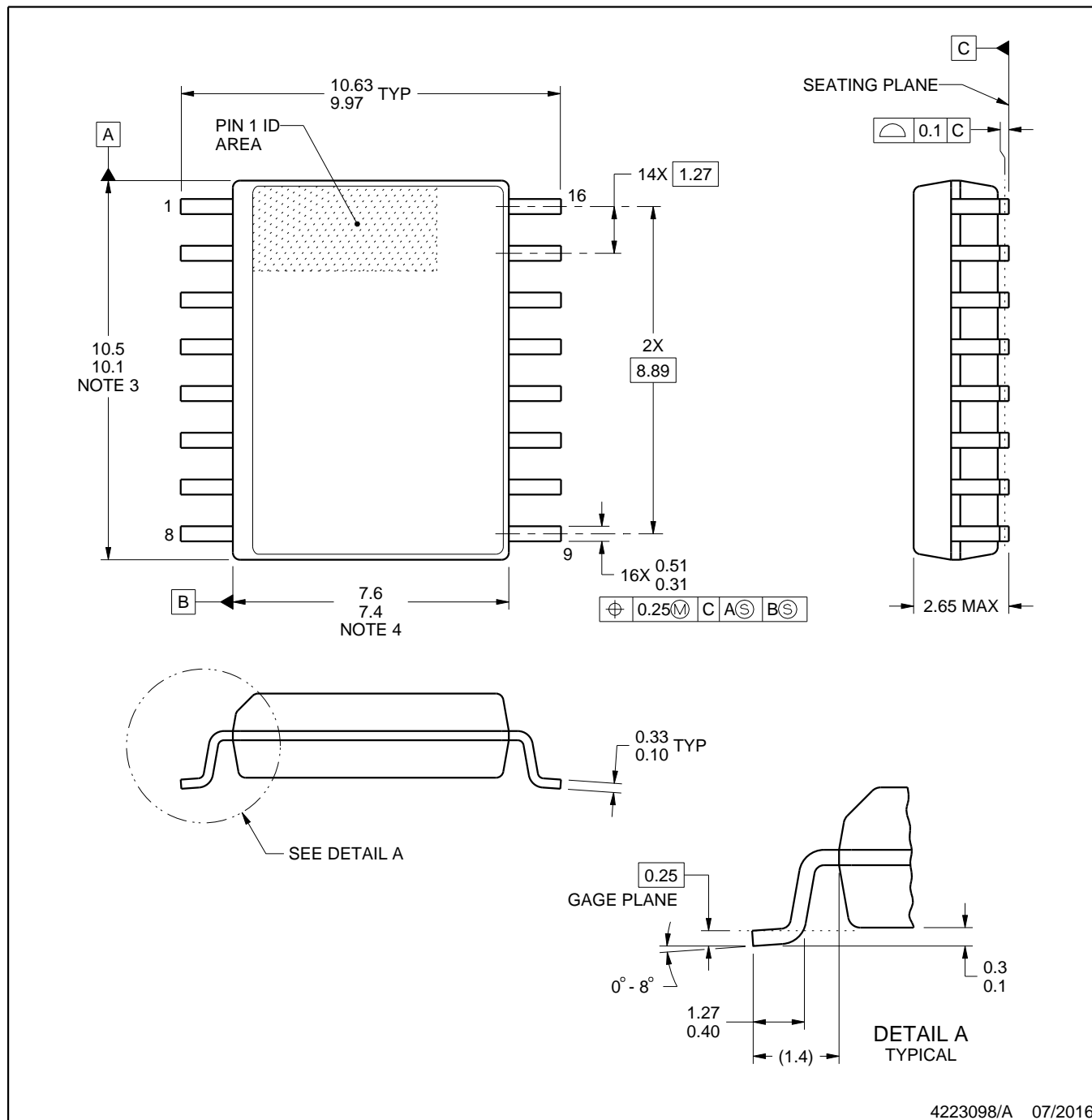
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
AMC3301DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
AMC3301DWE.A	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
AMC3301DWE4	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
AMC3301DWE4.A	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6



**DWE0016A**

# **PACKAGE OUTLINE** **SOIC - 2.65 mm max height**

SOIC



4223098/A 07/2016

## **NOTES:**

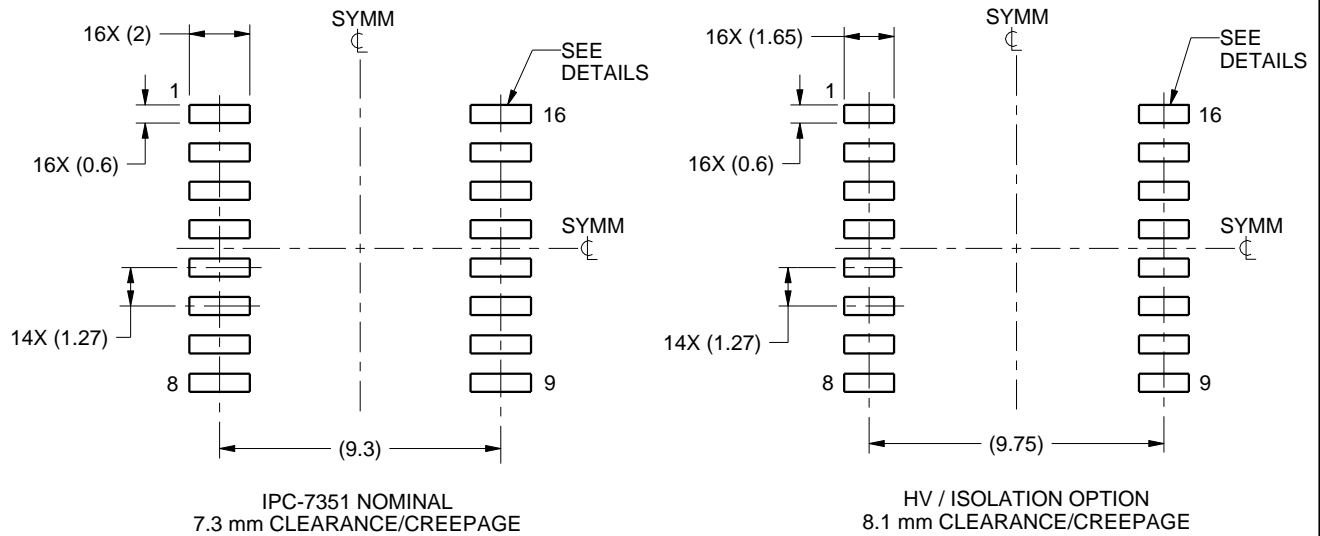
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

# EXAMPLE BOARD LAYOUT

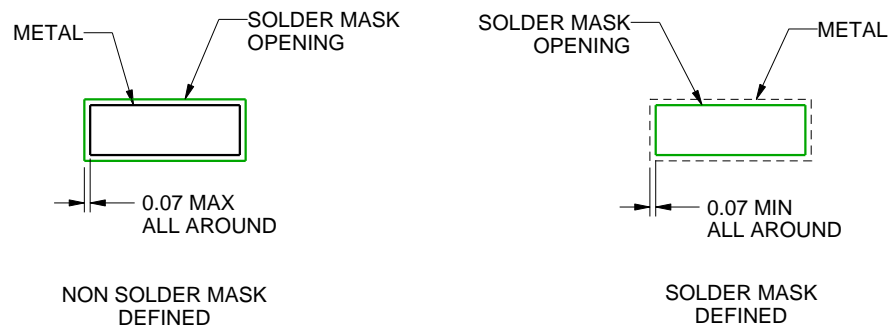
DWE0016A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE  
SCALE:4X



SOLDER MASK DETAILS

4223098/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

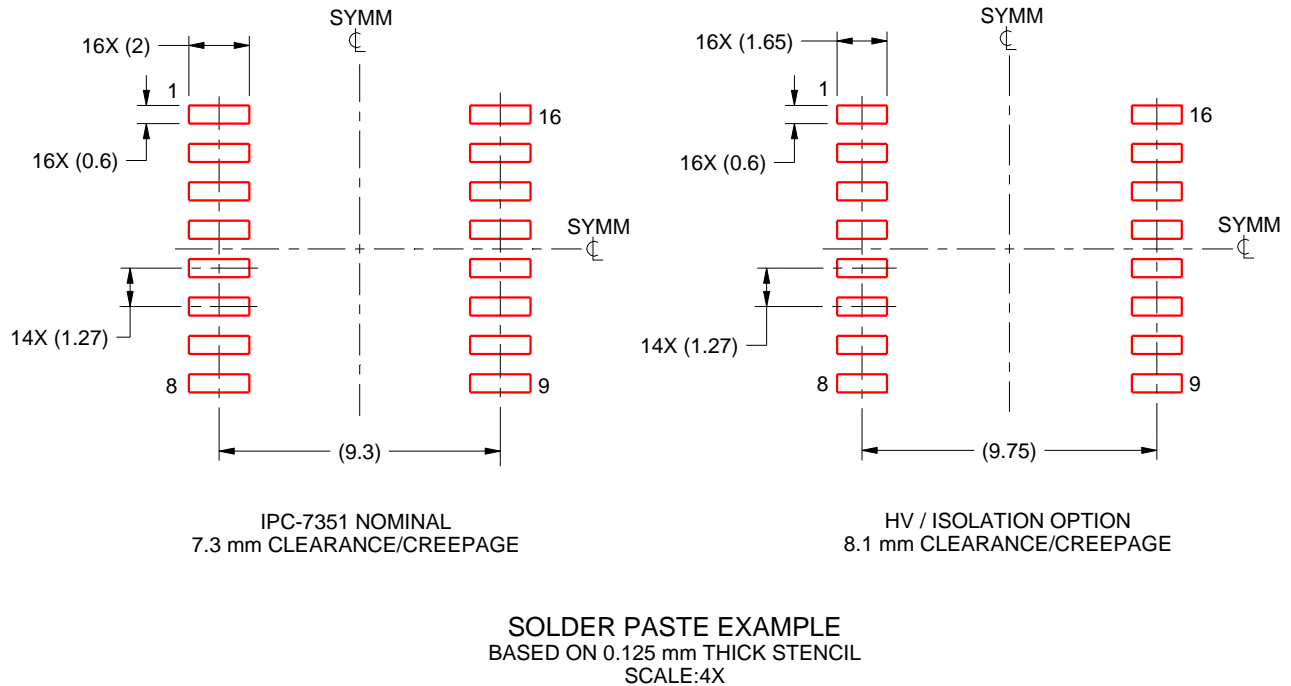
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DWE0016A

SOIC - 2.65 mm max height

SOIC



4223098/A 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



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